FLASH MEMORY

CMOS

32M (4M \times 8/2M \times 16) BIT Dual Operation

MBM29DL32XTD/BD-80/90/12

■ FEATURES

- 0.33 μm Process Technology
- Simultaneous Read/Write operations (dual bank)

Multiple devices available with different bank sizes (Refer to Table 1)

Host system can program or erase in one bank, then immediately and simultaneously read from the other bank Zero latency between read and write operations

Read-while-erase

Read-while-program

Single 3.0 V read, program, and erase
 Minimizes system level power requirement

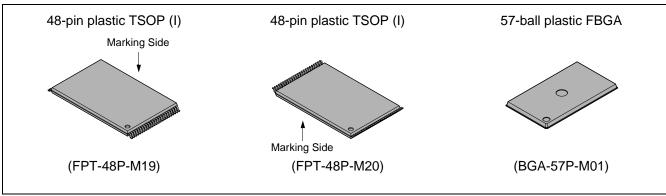
Minimizes system level power requirements

■ PRODUCT LINE UP

(Continued)

	Part N	lo.	MBM29DL32XTD/MBM29DL32XBD						
www.Da	Ordering Part No.	$Vcc = 3.3 V ^{+0.3 V}_{-0.3 V}$	80	_	_				
		$Vcc = 3.0 \text{ V} {}^{+0.6 \text{ V}}_{-0.3 \text{ V}}$	_	90	12				
		Time (ns)	80	90	120				
		e (ns)	80	90	120				
		e (ns)	30	35	50				

■ PACKAGES



Em\edded EraseTM and Embedded ProgramTM are trademarks of Advanced Micro Devices, Inc.

(Continued)

Compatible with JEDEC-standard commands

Uses same software commands as E2PROMs

• Compatible with JEDEC-standard world-wide pinouts

48-pin TSOP(I) (Package suffix: PFTN – Normal Bend Type, PFTR – Reversed Bend Type) 57-ball FBGA (Package suffix: PBT)

• Minimum 100,000 program/erase cycles

High performance

80 ns maximum access time

· Sector erase architecture

Eight 4K word and sixty-three 32K word sectors in word mode

Eight 8K byte and sixty-three 64K byte sectors in byte mode

Any combination of sectors can be concurrently erased. Also supports full chip erase.

• Boot Code Sector Architecture

T = Top sector

B = Bottom sector

• Hidden ROM (Hi-ROM) region

64K byte of Hi-ROM, accessible through a new "Hi-ROM Enable" command sequence Factory serialized and protected to provide a secure electronic serial number (ESN)

• WP/ACC input pin

At VIL, allows protection of boot sectors, regardless of sector protection/unprotection status

At VIH, allows removal of boot sector protection

At VACC, increases program performance

Embedded Erase[™] Algorithms

Automatically pre-programs and erases the chip or any sector

Embedded Program[™] Algorithms

Automatically writes and verifies data at specified address

• Data Polling and Toggle Bit feature for detection of program or erase cycle completion

Ready/Busy output (RY/BY)

www.DataSheHardware method for detection of program or erase cycle completion

Automatic sleep mode

When addresses remain stable, automatically switch themselves to low power mode.

- Low Vcc write inhibit ≤ 2.5 V
- Erase Suspend/Resume

Suspends the erase operation to allow a read data and/or program in another sector within the same device

Sector group protection

Hardware method disables any combination of sector groups from program or erase operations

- Sector Group Protection Set function by Extended sector group protection command
- Fast Programming Function by Extended Command
- Temporary sector group unprotection

Temporary sector group unprotection via the RESET pin.

• In accordance with CFI (Common Flash Memory Interface)

■ GENERAL DESCRIPTION

The MBM29DL32XTD/BD are a 32M-bit, 3.0 V-only Flash memory organized as 4M bytes of 8 bits each or 2M words of 16 bits each. The MBM29DL32XTD/BD are offered in a 48-pin TSOP(I) and FBGA Package. These devices are designed to be programmed in-system with the standard system 3.0 V Vcc supply. 12.0 V VPP and 5.0 V Vcc are not required for write or erase operations. The devices can also be reprogrammed in standard EPROM programmers.

MBM29DL32XTD/BD are organized into two banks, Bank 1 and Bank 2, which can be considered to be two separate memory arrays as far as certain operations are concerned. These devices are the same as Fujitsu's standard 3 V only Flash memories with the additional capability of allowing a normal non-delayed read access from a non-busy bank of the array while an embedded write (either a program or an erase) operation is simultaneously taking place on the other bank.

In the MBM29DL32XTD/BD, a new design concept is implemented, so called "Sliding Bank Architecture". Under this concept, the MBM29DL32XTD/BD can be produced a series of devices with different Bank 1/Bank 2 size combinations; 0.5 Mb/31.5 Mb, 4 Mb/28 Mb, 8 Mb/24 Mb, 16 Mb/16 Mb.

The standard MBM29DL32XTD/BD offer access times 80 ns, 90 ns and 120 ns, allowing operation of high-speed microprocessors without wait states. To eliminate bus contention the devices have separate chip enable (\overline{CE}) , write enable (\overline{WE}) , and output enable (\overline{OE}) controls.

The MBM29DL32XTD/BD are pin and command set compatible with JEDEC standard E²PROMs. Commands are written to the command register using standard microprocessor write timings. Register contents serve as input to an internal state-machine which controls the erase and programming circuitry. Write cycles also internally latch addresses and data needed for the programming and erase operations. Reading data out of the devices is similar to reading from 5.0 V and 12.0 V Flash or EPROM devices.

The MBM29DL32XTD/BD are programmed by executing the program command sequence. This will invoke the Embedded Program Algorithm which is an internal algorithm that automatically times the program pulse widths and verifies proper cell margin. Typically, each sector can be programmed and verified in about 0.5 seconds. Erase is accomplished by executing the erase command sequence. This will invoke the Embedded Erase Algorithm which is an internal algorithm that automatically preprograms the array if it is not already programmed before executing the erase operation. During erase, the devices automatically time the erase pulse widths and verify proper cell margin.

A sector is typically erased and verified in 1.0 second. (If already completely preprogrammed.)

The devices also feature a sector erase architecture. The sector mode allows each sector to be erased and reprogrammed without affecting other sectors. The MBM29DL32XTD/BD are erased when shipped from the factory.

The devices feature single 3.0 V power supply operation for both read and write functions. Internally generated and regulated voltages are provided for the program and erase operations. A low V_{CC} detector automatically inhibits write operations on the loss of power. The end of program or erase is detected by \overline{Data} Polling of DQ_7 , by the Toggle Bit feature on DQ_6 , or the RY/ \overline{BY} output pin. Once the end of a program or erase cycle has been completed, the devices internally reset to the read mode.

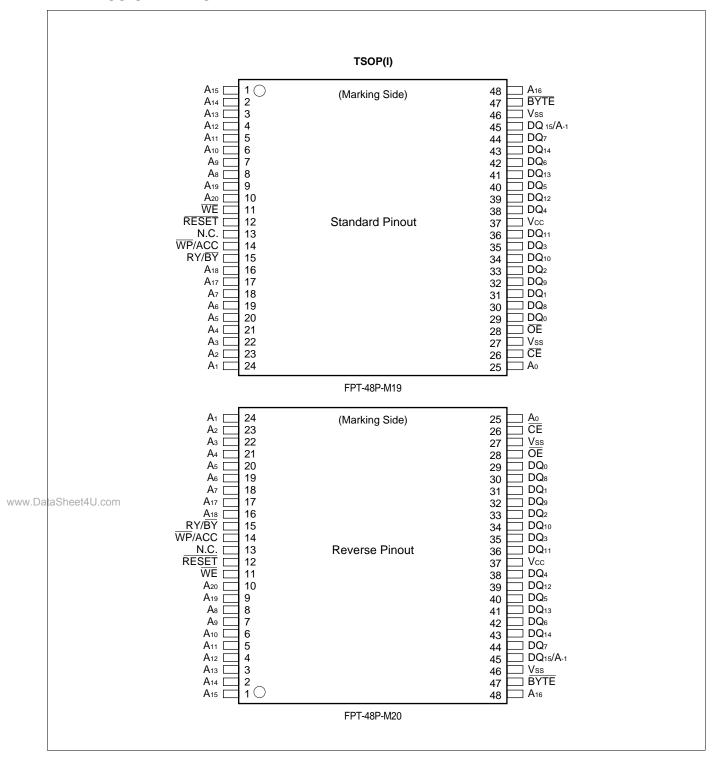
Fujitsu's Flash technology combines years of EPROM and E²PROM experience to produce the highest levels of quality, reliability, and cost effectiveness. The MBM29DL32XTD/BD memories electrically erase the entire chip or all bits within a sector simultaneously via Fowler-Nordhiem tunneling. The bytes/words are programmed one byte/word at a time using the EPROM programming mechanism of hot electron injection.

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Table 1 MBM29DL32XTD/BD Device Bank Divisions

Device	Organization		Bank 1	Bank 2		
Part Number	Organization	Megabits	Sector sizes	Megabits	Sector sizes	
MBM29DL321TD/BD		0.5 Mbit	Eight 8K byte/4K word	31.5 Mbit	Sixty-three 64K byte/32K word	
MBM29DL322TD/BD		4 Mbit	Eight 8K byte/4K word, seven 64K byte/32K word	28 Mbit	Fifty-six 64K byte/32K word	
MBM29DL323TD/BD	× 8/× 16	8 Mbit	Eight 8K byte/4K word, fifteen 64K byte/32K word	24 Mbit	Forty-eight 64K byte/32K word	
MBM29DL324TD/BD		16 Mbit	Eight 8K byte/4K word, thirty-one 64K byte/ 32K word	16 Mbit	Thirty-two 64K byte/32K word	

■ PIN ASSIGNMENTS



(Continued)

FBGA

(TOP VIEW)
Marking side

$$(\widehat{C1}),(\widehat{C2}),(\widehat{C3}),(\widehat{C4}),(\widehat{C5}),(\widehat{C6})$$

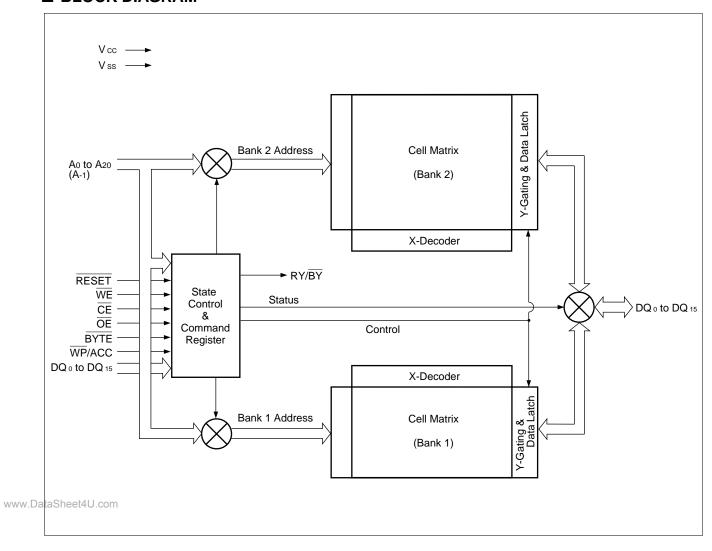
(BGA-57P-M01)

	A1	A ₃	A2	A ₇	A3	RY/BY	A4	WE	A5	A 9	A6	A ₁₃
	B1	A ₄	B2	A ₁₇	В3	WP/ACC	B4	RESET	B5	A 8	B6	A ₁₂
	C1	A ₂	C2	A ₆	C3	A ₁₈	C4	N.C.	C5	A ₁₀	C6	A ₁₄
Sh	P1 _{U.c}	o A 1	D2	A ₅	D3	A ₂₀	D4	A ₁₉	D5	A ₁₁	D6	A 15
	E1	A ₀	E2	DQ ₀	E3	DQ ₂	E4	DQ₅	E5	DQ ₇	E6	A ₁₆
	F1	CE	F2	DQ ₈	F3	DQ ₁₀	F4	DQ ₁₂	F5	DQ ₁₄	F6	BYTE
	G1	OE	G2	DQ ₉	G3	DQ ₁₁	G4	Vcc	G5	DQ ₁₃	G6	DQ ₁₅ /A ₋₁
	H1	Vss	H2	DQ ₁	Н3	DQ ₃	H4	DQ ₄	H5	DQ ₆	H6	Vss

Regarding additional No Internal Connection balls, please contact a Fujitsu representative for more information.

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■ BLOCK DIAGRAM



■ LOGIC SYMBOL

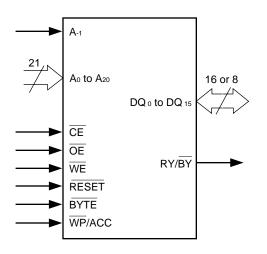


Table 2 MBM29DL32XTD/BD Pin Configuration

Pin	Function
A-1, A ₀ to A ₂₀	Address Inputs
DQ ₀ to DQ ₁₅	Data Inputs/Outputs
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
RY/ BY	Ready/Busy Output
RESET	Hardware Reset Pin/Temporary Sector Group Unprotection
BYTE	Selects 8-bit or 16-bit mode
WP/ACC	Hardware Write Protection/Program Acceleration
N.C.	No Internal Connection
Vss	Device Ground
Vcc	Device Power Supply

■ DEVICE BUS OPERATION

Table 3 MBM29DL32XTD/BD User Bus Operations (BYTE = VIH)

Operation	CE	ΘE	WE	Αo	A 1	A 6	A 9	DQ ₀ to DQ ₁₅	RESET	WP/ACC
Auto-Select Manufacturer Code (1)	L	L	Н	L	L	L	VID	Code	Н	Х
Auto-Select Device Code (1)	L	L	Н	Τ	L	L	VID	Code	Н	Х
Read (3)	L	L	Н	A ₀	A ₁	A 6	A 9	D ouт	Н	Х
Standby	Н	Х	Χ	Χ	Х	Χ	Х	HIGH-Z	Н	Х
Output Disable	L	Н	Н	Χ	Х	Х	Х	HIGH-Z	Н	Х
Write (Program/Erase)	L	Н	L	A ₀	A 1	A 6	A 9	Din	Н	Х
Enable Sector Group Protection (2), (4)	L	VID	T	L	Н	L	VID	Х	Н	Х
Verify Sector Group Protection (2), (4)	L	L	Н	L	Н	L	VID	Code	Н	Х
Temporary Sector Group Unprotection (5)	Χ	Х	Х	Χ	Х	Х	Х	Х	VID	Х
Reset (Hardware)/Standby	Х	Х	Х	Χ	Χ	Χ	Х	HIGH-Z	L	Х
Boot Block Sector Write Protection	Χ	Х	Χ	Χ	Х	Χ	Χ	Х	Х	L

Table 4 MBM29DL32XTD/BD User Bus Operations (BYTE = V_{IL})

Operation	CE	ŌΕ	WE	DQ ₁₅ / A-1	Ao	A 1	A 6	A 9	DQ ₀ to DQ ₇	RESET	WP/ACC
Auto-Select Manufacturer Code (1)	L	L	Н	L	L	L	L	VID	Code	Н	Х
Auto-Select Device code (1)	L	L	Н	L	Н	L	L	VID	Code	Н	Х
Read (3)	L	L	Н	A -1	A_0	A 1	A_6	A 9	D оит	Н	Х
Standby	Н	Х	Χ	Х	Χ	Χ	Χ	Χ	HIGH-Z	Н	Х
Output Disable	L	Н	Н	Х	Χ	Х	Χ	Χ	HIGH-Z	Н	Х
Write (Program/Erase)	L	Н	L	A -1	A_0	A 1	A_6	A 9	DiN	Н	Х
Enable Sector Group Protection (2), (4)	L	VID	L	L	L	Н	L	VID	Х	Н	Х
Verify Sector Group Protection (2), (4)	L	L	Н	L	L	Н	L	VID	Code	Н	Х
Temporary Sector Group Unprotection (5)	Х	Х	Х	Х	Х	Х	Х	Х	Х	VID	Х
Reset (Hardware)/Standby	Χ	Χ	Χ	Х	Χ	Χ	Χ	Χ	HIGH-Z	L	Х
Boot Block Sector Write Protection	Χ	Χ	Χ	Х	Χ	Χ	Χ	Χ	X	Х	L

Legend: L = V_{IL} , H = V_{IH} , X = V_{IL} or V_{IH} , $\Box \Box$ = Pulse input. See DC Characteristics for voltage levels.

- Notes: 1. Manufacturer and device codes may also be accessed via a command register write sequence. See Table 12.
 - 2. Refer to the section on Sector Group Protection.
 - 3. $\overline{\text{WE}}$ can be V_{IL} if $\overline{\text{OE}}$ is V_{IL} , $\overline{\text{OE}}$ at V_{IH} initiates the write operations.
 - 4. $Vcc = 3.3 V \pm 10\%$
 - 5. It is also used for the extended sector group protection.

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9

■ ABSOLUTE MAXIMUM RATINGS(See WARNING)

Parameter	Symbol	Conditions	Rat	Max. +125 +85 Vcc+0.5 +4.0 +13.0 +10.5	Unit
raiailletei	Syllibol	Conditions	Min.		Oilit
Storage Temperature	Tstg	_	– 55	+125	°C
Ambient Temperature with Power Applied	TA	_	-40	+85	°C
Voltage with Respect to Ground All pins except A ₉ , OE, RESET (Note 1)	VIN, VOUT	_	-0.5	Vcc+0.5	V
Power Supply Voltage (Note 1)	Vcc	_	-0.5	+4.0	V
A ₉ , OE , and RESET (Note 2)	Vin	_	-0.5	+13.0	V
WP/ACC (Note 3)	VIN	_	-0.5	+10.5	V

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

- Notes: 1. Minimum DC voltage on input or I/O pins are -0.5 V. During voltage transitions, inputs may negative overshoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC voltage on output and I/O pins are Vcc +0.5 V. During voltage transitions, outputs may positive overshoot to Vcc +2.0 V for periods of up to 20 ns.
 - 2. Minimum DC input voltage on A₉, \overline{OE} and \overline{RESET} pins are -0.5 V. During voltage transitions, A₉, \overline{OE} and \overline{RESET} pins may negative overshoot V_{SS} to -2.0 V for periods of up to 20 ns. Maximum DC input voltage on A₉, \overline{OE} and \overline{RESET} pins are +13.0 V which may positive overshoot to 14.0 V for periods of up to 20 ns. when V_{CC} is applied.
- 3. Minimum DC input voltage on WP/ACC pin is -0.5 V. During voltage transitions, WP/ACC pin may negative overshoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC input voltage on WP/ACC pin iis +10.5V which may positive overshoot to +10.5V for periods of up to 20ns when Vcc is applied.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Conditions	Va	Unit	
raiailletei	Syllibol	Conditions	Min.	Max.	Oille
Ambient Temperature	TA	MBM29DL32XTD/BD-80	-20	+70	°C
Ambient Temperature	IA	MBM29DL32XTD/BD-90/12	-40		°C
Power Supply Voltage	Ves	MBM29DL32XTD/BD-80	+3.0	+3.6	V
Power Supply Voltage	Vcc	MBM29DL32XTD/BD-90/12	+2.7	+3.6	V

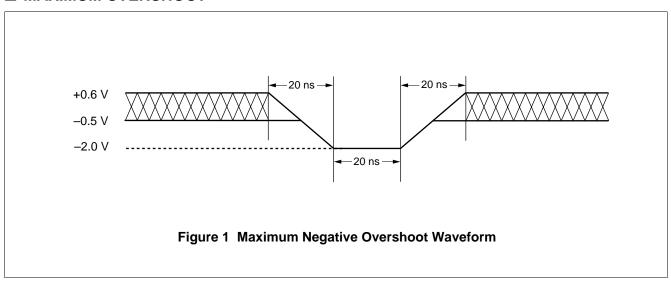
Operating ranges define those limits between which the functionality of the devices are guaranteed.

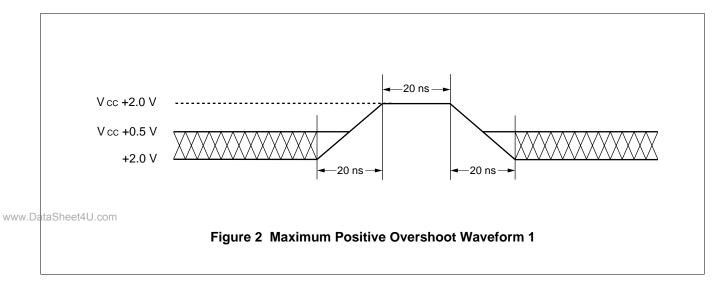
WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

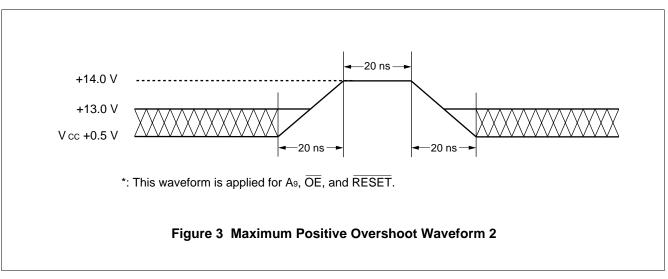
Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ MAXIMUM OVERSHOOT







■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

Doromotor	Cumbal	Conditions		Va	lue	Unit
Parameter	Symbol	Conditions		Min.	Max.	Unii
Input Leakage Current	Iu	VIN = Vss to Vcc, Vcc = Vcc	-1.0	+1.0	μΑ	
Output Leakage Current	Іьо	Vout = Vss to Vcc, Vcc = V	cc Max.	-1.0	+1.0	μΑ
A ₉ , OE, RESET Inputs Leakage Current	Ішт	Vcc = Vcc Max. A ₉ , OE, RESET = 12.5 V		_	35	μΑ
		CE = V _I , OE = V _I ,	Byte		16	т Л
Vec Active Current (Note 1)	laa.	f = 5 MHz	Word	_	18	mA
Vcc Active Current (Note 1)	Icc1	CE = VIL, OE = VIH,	Byte		7	m/
		f = 1 MHz	Word		7	111/-
Vcc Active Current (Note 2)	Icc2	CE = VIL, OE = VIH		_	35	m/
Vcc Current (Standby)	Іссз	$\frac{V_{CC} = V_{CC} \text{ Max., } \overline{CE} = V_{CC}}{\text{RESET}} = V_{CC} \pm 0.3 \text{ V}$	± 0.3 V,	_	5	μΑ
Vcc Current (Standby, Reset)	Icc4	Vcc = Vcc Max., WE/ACC = 0.3 V, RESET = Vss ± 0.3		_	5	μΑ
Vcc Current (Automatic Sleep Mode) (Note 3)	Icc5	$\frac{\text{Vcc} = \text{Vcc Max., } \overline{\text{CE}} = \text{Vss}}{\text{RESET}} = \text{Vcc} \pm 0.3 \text{ V}$ $\text{Vin} = \text{Vcc} \pm 0.3 \text{ V or Vss} \pm$		_	5	μΑ
Vcc Active Current (Note 5)		<u> </u>	Byte	_	51	/
(Read-While-Program)	Icc ₆	$\overline{CE} = V_{IL}, \overline{OE} = V_{IH}$	Word	_	53	m/
Vcc Active Current (Note 5)	laa-	CE = VIL, OE = VIH	Byte	_	51	m/
(Read-While-Erase)	Icc7	GE = VIL, GE = VIH	Word	_	53	m/
Vsc Active Current (Erase-Suspend-Program)	Icc8	$\overline{CE} = V_{IL}, \overline{OE} = V_{IH}$		_	35	m/
ACC Accelerated Program Current	lacc	Vcc = Vcc Max. WP/ACC = Vacc Max.		_	20	m <i>P</i>
Input Low Level	VIL	_		-0.5	0.6	V
Input High Level	ViH	_		2.0	Vcc+0.3	V
Voltage for WP/ACC Sector Protection/Unprotection and Program Acceleration	Vacc	_		8.5	9.5	V
Voltage for Autoselect and Sector Protection (A ₉ , OE, RESET) (Note 4)	VID	_		11.5	12.5	V

(Continued)

Notes: 1. The lcc current listed includes both the DC operating current and the frequency dependent component.

- 2. \mbox{lcc} active while Embedded Algorithm (program or erase) is in progress.
- 3. Automatic sleep mode enables the low power mode when address remain stable for 150 ns.
- 4. Applicable for only Vcc applying.
- 5. Embedded Algorithm (program or erase) is in progress. (@5 MHz)

12

(Continued)

Parameter	Symbol	Conditions	Va	Unit	
Farameter	Зуньон	Conditions	Min.	Max.	Offic
Output Low Voltage Level	Vol	IoL = 4.0 mA, Vcc = Vcc Min.	_	0.45	V
Output High Voltage Level	V _{OH1}	/oL $I_{OL} = 4.0 \text{ mA}, V_{CC} = V_{CC} \text{ Min.}$ — 0.45 /oH1 $I_{OH} = -2.0 \text{ mA}, V_{CC} = V_{CC} \text{ Min.}$ 2.4 — I_{OH2} $I_{OH} = -100 \text{ μA}$ $V_{CC} = 0.4$ —	V		
Output High voltage Level	V _{OH2}	Іон = –100 μА	Vcc-0.4	Max. 0.45 —	V
Low Vcc Lock-Out Voltage	Vlko	_	2.3	2.5	V

Notes: 1. The loc current listed includes both the DC operating current and the frequency dependent component.

- 2. Icc active while Embedded Algorithm (program or erase) is in progress.
- 3. Automatic sleep mode enables the low power mode when address remain stable for 150 ns.
- 4. Applicable for only Vcc applying.
- 5. Embedded Algorithm (program or erase) is in progress. (@5 MHz)

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2. AC Characteristics

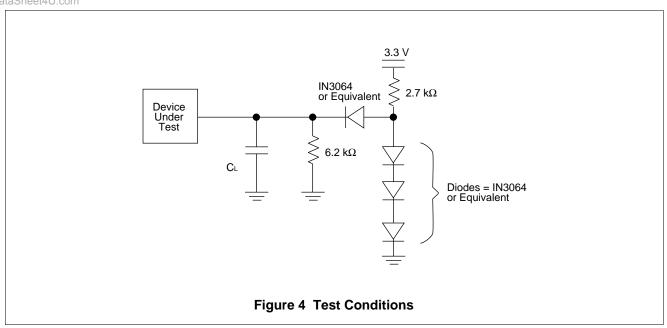
• Read Only Operations Characteristics

	meter ibols	Description	Test se	etup	80 (Note)	90 (Note)	12 (Note)	Unit
JEDEC	Standard	•		•	(Note)	(Note)	(Note)	
tavav	t RC	Read Cycle Time	_	Min.	80	90	120	ns
tavqv	tacc	Address to Output Delay	CE = VIL OE = VIL	Max.	80	90	120	ns
t ELQV	tce	Chip Enable to Output Delay	OE = VIL	Max.	80	90	120	ns
t GLQV	toe	Output Enable to Output Delay	_	Max.	30	35	50	ns
t ehqz	t DF	Chip Enable to Output High-Z	_	Max.	25	30	30	ns
t GHQZ	t DF	Output Enable to Output High-Z	_	Max.	25	30	30	ns
taxqx	tон	Output Hold Time from Addresses, CE or OE, Whichever Occurs First	_	Min.	0	0	0	ns
_	t READY	RESET Pin Low to Read Mode	_	Max.	20	20	20	μs
_	telfl telfh	CE or BYTE Switching Low or High	_	Max.	5	5	5	ns

Note: Test Conditions:
Output Load: 1 TTL gate and 30 pF (MBM29DL32XTD/BD 80)
1 TTL gate and 100 pF (MBM29DL32XTD/BD 90/12)

Input rise and fall times: 5 ns Input pulse levels: 0.0 V to 3.0 V Timing measurement reference level

Input: 1.5 V Output:1.5 V



• Write/Erase/Program Operations

tavav twc tavwl tas — taso twlax tah — taht tbvwh tbs twhdx tbh — toeh — tceph tghwl tghwl tghwl tghwl tghwl tghwl tghwl tghwl tghwl tcs twlel tws twlel twh twlel twh twlel twh twlel twh twh twh </th <th>er symbols</th> <th></th> <th>Docarintian</th> <th></th> <th>80</th> <th>90</th> <th>12</th> <th>Unit</th>	er symbols		Docarintian		80	90	12	Unit
JEDEC	Standard	- 	Description		80	90	12	Uni
tavav	twc	Write Cycle Tim	ne	Min.	80	90	120	ns
t avwl	t AS	Address Setup	Time	Min.	0	0	0	ns
_	taso	Address Setup Toggle Bit Pollin	Time to OE Low During	Min.	12	15	15	ns
twlax	t ah	Address Hold T	ddress Hold Time		45	45	50	ns
_	t AHT	Address Hold T During Toggle E	ime from CE or OE High Bit Polling	Min.	0	0	0	ns
t DVWH	t DS	Data Setup Tim	е	Min.	30	35	50	ns
t whdx	t DH	Data Hold Time		Min.	0	0	0	ns
		Output Enable	Read	Min.	0	0	0	ns
_	t oeh	Hold Time	Toggle and Data Polling	Min.	10	10	10	ns
_	t CEPH	CE High During	Toggle Bit Polling	Min.	20	20	20	ns
_	t oeph	OE High During	Toggle Bit Polling	Min.	20	20	20	ns
t GHWL	t GHWL	Read Recover	Γime Before Write	Min.	0	0	0	ns
t GHEL	t GHEL	Read Recover	Γime Before Write	Min.	0	0	0	ns
t ELWL	t cs	CE Setup Time		Min.	0	0	0	ns
twlel	tws	WE Setup Time	,	Min.	0	0	0	ns
twheh	tсн	CE Hold Time		Min.	0	0	0	ns
	от t wн	WE Hold Time		Min.	0	0	0	ns
tww	t wp	Write Pulse Wid	dth	Min.	35	35	50	ns
teleh	t CP	CE Pulse Width	1	Min.	35	35	50	ns
t whwL	twpн	Write Pulse Wid	dth High	Min.	25	30	30	ns
t ehel	t cpH	CE Pulse Width	High	Min.	25	30	30	ns
t whwh1	t whwh1	Byte Programm	ing Operation	Тур.	8	8	8	μs
t whwh2	t whwh2	Sector Erase O	peration (Note 1)	Тур.	1	1	1	sec
_	tvcs	Vcc Setup Time		Min.	50	50	50	μs
_	tvidr	Rise Time to VII	(Note 2)	Min.	500	500	500	ns
_	tvaccr	Rise Time to VII	(Note 2)	Min.	500	500	500	ns
_	t vlht	Voltage Transition	on Time (Note 2)	Min.	4	4	4	μs
	twpp	Write Pulse Wid	dth (Note 2)	Min.	100	100	0 15 50 0 0 0 0 10 20 20 0 0 0 0 0 0 0 0 0 50 50 30 30 30 8 1 50 50 50 50 50 50 50 50 50 50 50 50 50	μs
_	toesp	OE Setup Time	to WE Active (Note 2)	Min.	4	4	4	μs

(Continued)

(Continued)

Paramete	r symbols	Description		80	90	12	Unit
JEDEC	Standard	Description		00	90	12	Onit
_	tcsp	CE Setup Time to WE Active (Note 2)	Min.	4	4	4	μs
_	t RB	Recover Time from RY/BY	Min.	0	0	0	ns
_	t RP	RESET Pulse Width	Min.	500	500	500	ns
_	t RH	RESET High Level Period before Read	Min.	200	200	200	ns
_	t FLQZ	BYTE Switching Low to Output High-Z	Max.	30	30	40	ns
_	t FHQV	BYTE Switching High to Output Active	Max.	80	90	120	ns
_	t BUSY	Program/Erase Valid to RY/BY Delay	Max.	90	90	90	ns
_	t eoe	Delay Time from Embedded Output Enable	Max.	80	90	120	ns
_	t TOW	Erase Time-Out Time	Min.	50	50	50	μs
_	tspd	Erase Suspend Transition Time	Max.	20	20	20	μs

Notes: 1. This does not include the preprogramming time.

2. This timing is for Sector Group Protection operation.

■ ERASE AND PROGRAMMING PERFORMANCE

Parameter		Limits		Unit	Comments		
Parameter	Min.	Тур.	Max.	Unit	Comments		
Sector Erase Time	_	1	10	sec	Excludes programming time prior to erasure		
Word Programming Time	_	16	360	μs	Excludes system-level		
Byte Programming Time	_	8	300	μs	overhead		
Chip Programming Time	_	_	100	sec	Excludes system-level overhead		
Program/Erase Cycle	100,000	_	_	cycles	_		

■ PIN CAPACITANCE

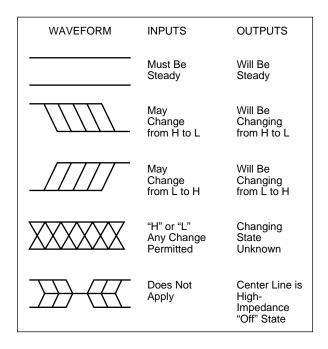
Parameter symbol	Parameter description	Test setup	Тур.	Max.	Unit
Cin	Input Capacitance	V _{IN} = 0	6	7.5	pF
Соит	Output Capacitance	Vоит = 0	8.5	12	pF
C _{IN2}	Control Pin Capacitance	V _{IN} = 0	8	11	pF
Сімз	WP/ACC Pin Capacitance	V _{IN} = 0	21.5	22.5	pF

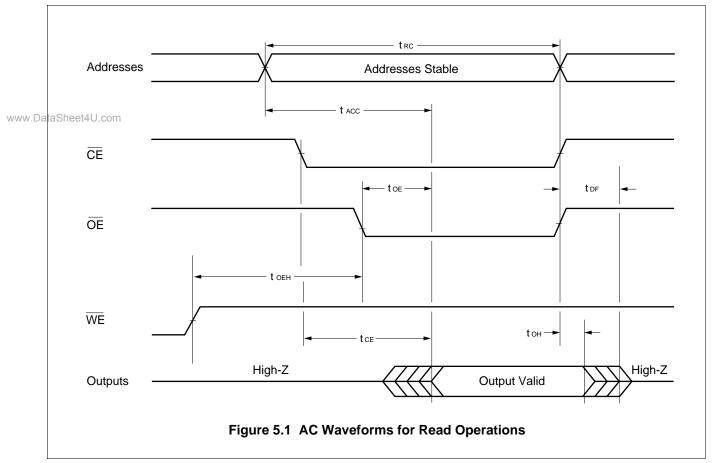
Note: Test conditions T_A = 25°C, f = 1.0 MHzs

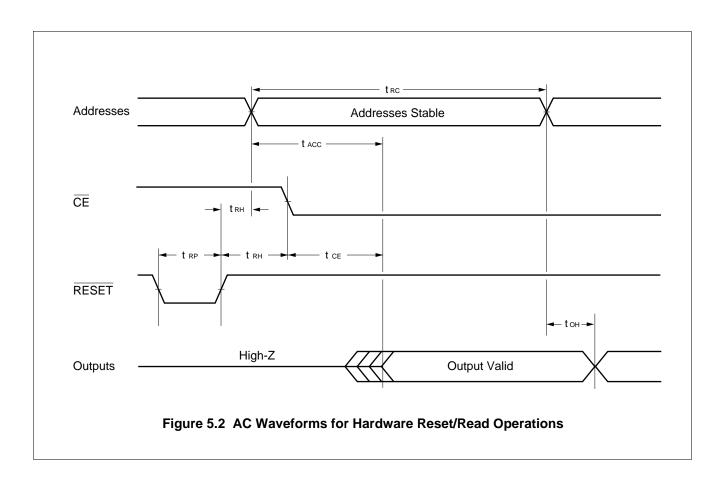
www. Data Sheet 4U.com

■ TIMING DIAGRAM

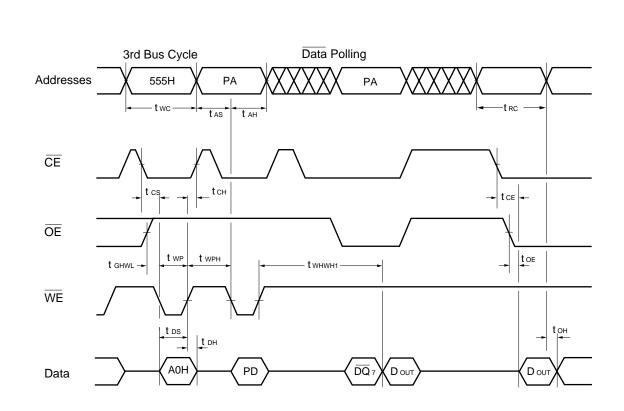
• Key to Switching Waveforms







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Notes: 1. PA is address of the memory location to be programmed.

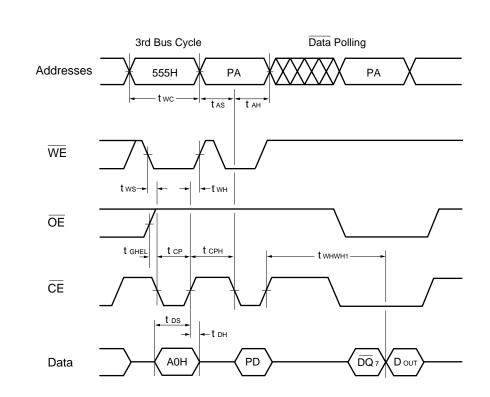
- 2. PD is data to be programmed at byte address.
- 3. $\overline{DQ_7}$ is the output of the complement of the data written to the device.
- 4. Dout is the output of the data written to the device.

5. Figure indicates last two bus cycles out of four bus cycle sequence.

6. These waveforms are for the ×16 mode. (The addresses differ from ×8 mode.)

Figure 6 AC Waveforms for Alternate $\overline{\text{WE}}$ Controlled Program Operations

20



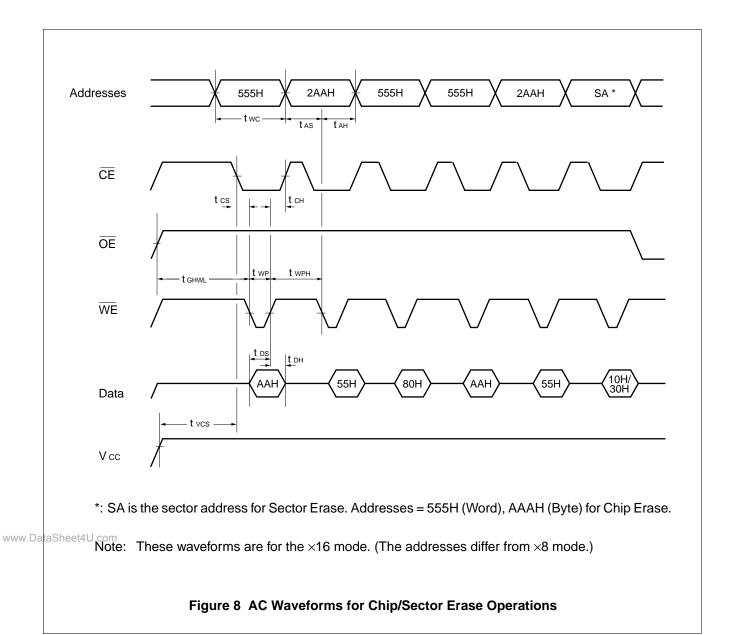
Notes: 1. PA is address of the memory location to be programmed.

- 2. PD is data to be programmed at byte address.
- 3. $\overline{DQ_7}$ is the output of the complement of the data written to the device.
- 4. Dout is the output of the data written to the device.

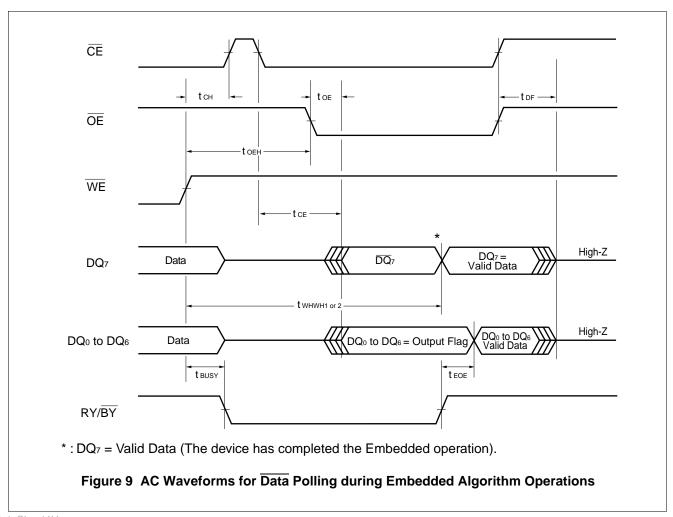
5. Figure indicates last two bus cycles out of four bus cycle sequence. www.DataSheet4U.com

6. These waveforms are for the ×16 mode. (The addresses differ from ×8 mode.)

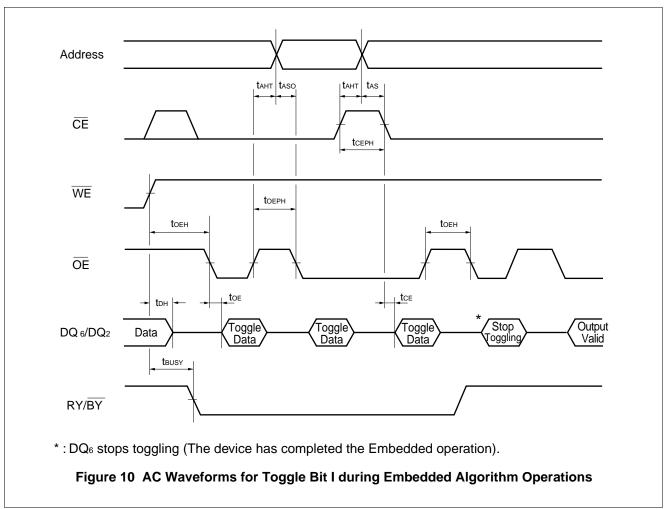
Figure 7 AC Waveforms for Alternate CE Controlled Program Operations

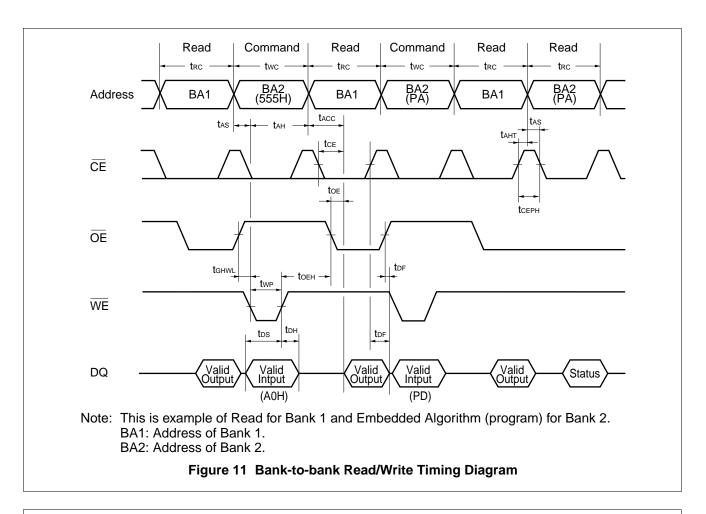


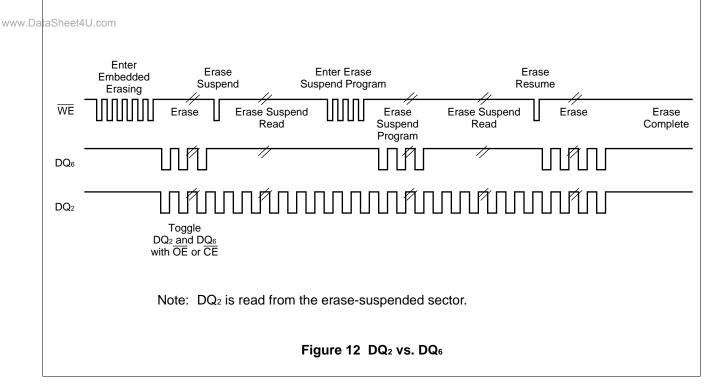
22

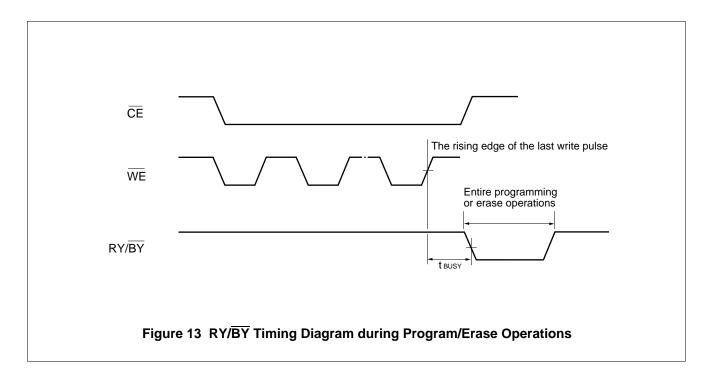


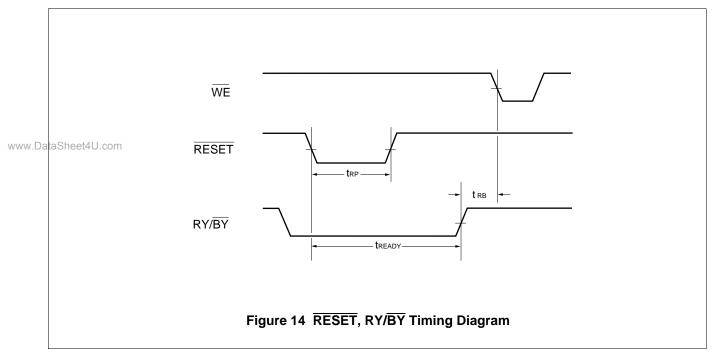
www. Data Sheet 4U.com

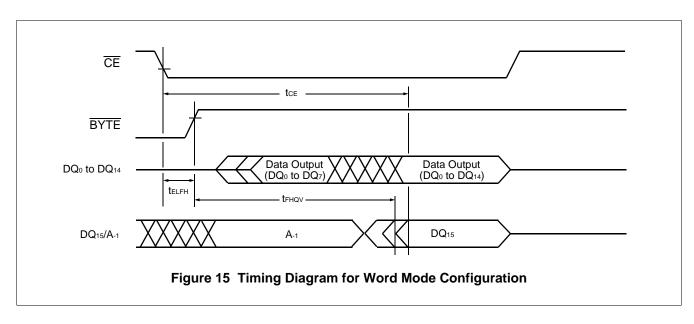


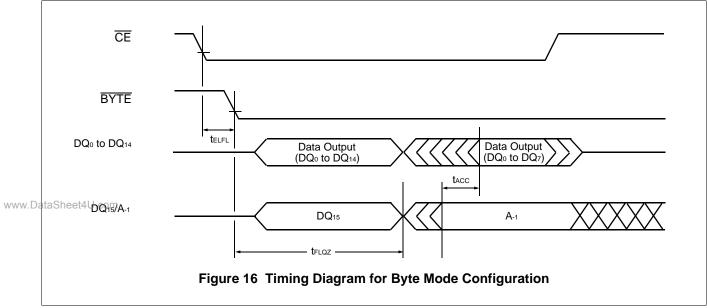


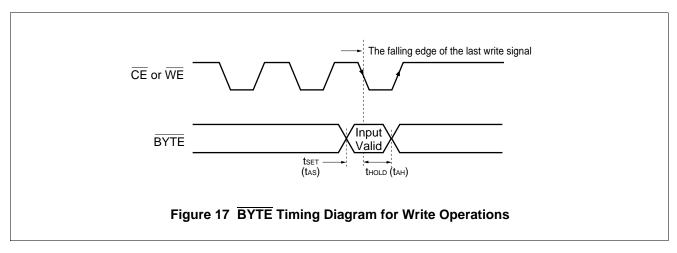


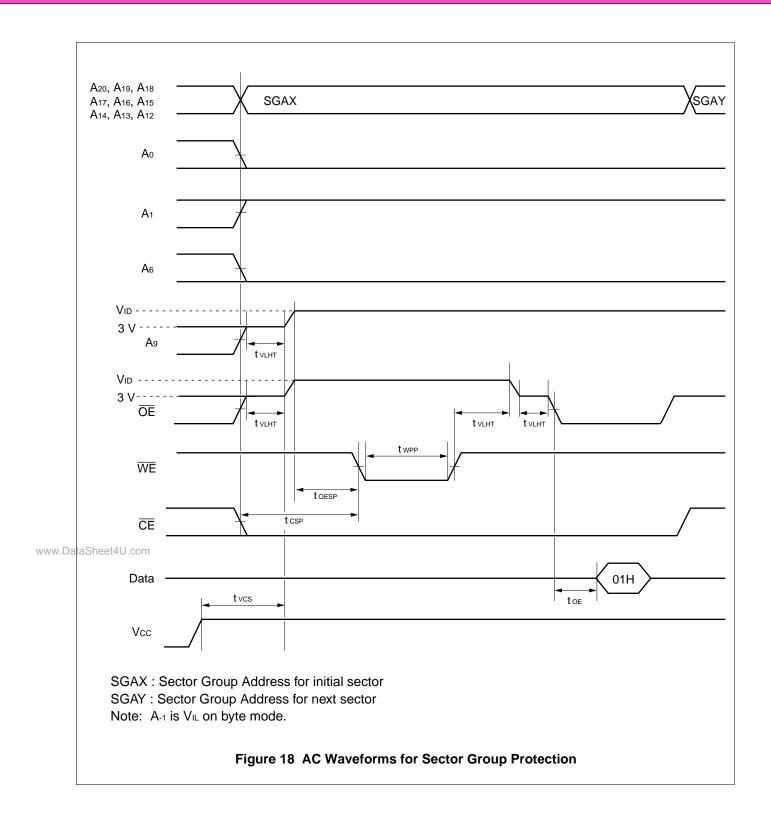


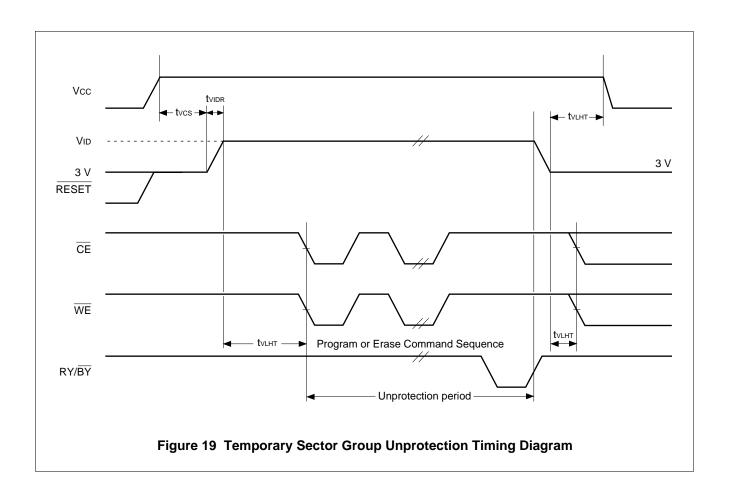


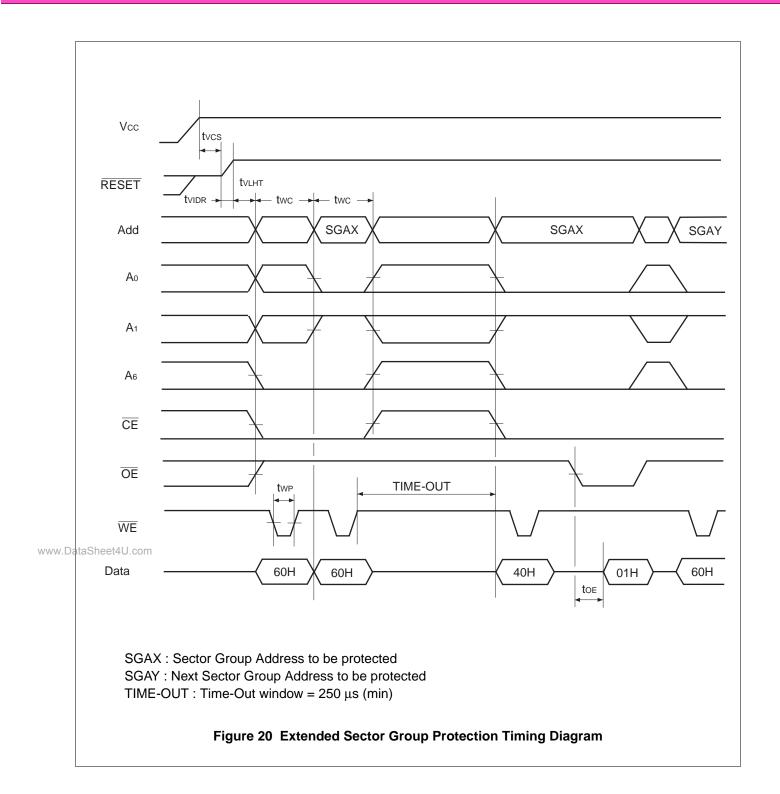


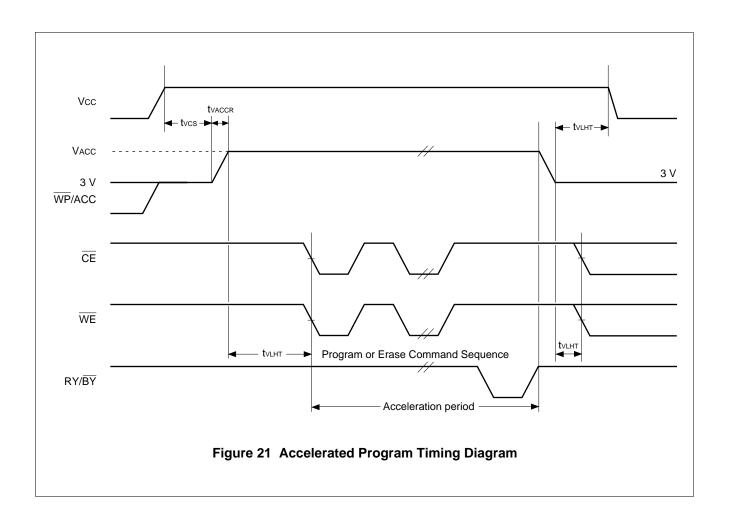












■ FLEXIBLE SECTOR-ERASE ARCHITECTURE

Table 5.1 Sector Address Tables (MBM29DL321TD)

					Sec	tor a	add	ress				Sector		
Bank	Bank Sector		Ва								Size	(×8) Address range	(×16) Address range	
		A ₂₀	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Address range
	SA0	0	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	00000H to 0FFFFH	000000H to 007FFFH
	SA1	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	10000H to 1FFFFH	008000H to 00FFFFH
	SA2	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	20000H to 2FFFFH	010000H to 017FFFH
	SA3	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	30000H to 3FFFFH	018000H to 01FFFFH
	SA4	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	40000H to 4FFFFH	020000H to 027FFFH
	SA5	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	50000H to 5FFFFH	028000H to 02FFFFH
	SA6	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	60000H to 6FFFFH	030000H to 037FFFH
	SA7	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	70000H to 7FFFFH	038000H to 03FFFFH
	SA8	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	80000H to 8FFFFH	040000H to 047FFFH
	SA9	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	90000H to 9FFFFH	048000H to 04FFFFH
	SA10	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	A0000H to AFFFFH	050000H to 057FFFH
	SA11	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	B0000H to BFFFFH	058000H to 05FFFFH
	SA12	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	C0000H to CFFFFH	060000H to 067FFFH
	SA13	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	D0000H to DFFFFH	068000H to 06FFFFH
	SA14	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	E0000H to EFFFFH	070000H to 077FFFH
	SA15	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	F0000H to FFFFFH	078000H to 07FFFFH
	SA16	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
Bank 2	SA17	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA18	0	1	0	0	1	0	Χ	Χ	Χ	Х	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA19	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA20	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA21	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
www.DataSheet4	SA22	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
	SA23	0	1	0	1	1	1	Χ	Χ	Χ	Х	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA24	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA25	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA26	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA27	0	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA28	0	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH
	SA29	0	1	1	1	0	1	Χ	Χ	Χ	Х	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
	SA30	0	1	1	1	1	0	Χ	Χ	Х	Х	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
	SA31	0	1	1	1	1	1	Χ	Χ	Х	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH
	SA32	1	0	0	0	0	0	Χ	Χ	Х	Х	64/32	200000H to 20FFFFH	100000H to 107FFFH
	SA33	1	0	0	0	0	1	Χ	Х	Х	Х	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	SA34	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH

(Continued)

(Continued)

WWW

				;	Sec	tor a	add	ress	3			Sector	(0)	(40)
Bank	Sector		Baı	nk a	ddre	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20		A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)		ſ
	SA35	1	Χ	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	SA36	1	Χ	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	SA37	1	Χ	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	SA38	1	Χ	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	SA39	1	Χ	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	SA40	1	Χ	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
	SA41	1	Χ	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
	SA42	1	Χ	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
	SA43	1	Χ	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	SA44	1	Χ	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
	SA45	1	Χ	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	SA46	1	Χ	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
	SA47	1	Χ	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
Bank 2	SA48	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
Dalik Z	SA49	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
	SA50	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	SA51	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
	SA52	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
	SA53	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	SA54	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	SA55	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	SA56	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	SA57	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
DataShe	SA58	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
	SA59	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	SA60	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH
	SA61	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	SA62	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000H to 3F1FFFH	1F8000H to 1F8FFFH
	SA64	1	1	1	1	1	1	0	0	1	Χ	8/4	3F2000H to 3F3FFFH	1F9000H to 1F9FFFH
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000H to 3F5FFFH	1FA000H to 1FAFFFH
Don't 4	SA66	1	1	1	1	1	1	0	1	1	Χ	8/4	3F6000H to 3F7FFFH	1FB000H to 1FBFFFH
Bank 1	SA67	1	1	1	1	1	1	1	0	0	Χ	8/4	3F8000H to 3F9FFFH	1FC000H to 1FCFFFH
	SA68	1	1	1	1	1	1	1	0	1	Χ	8/4	3FA000H to 3FBFFFH	1FD000H to 1FDFFFH
	SA69	1	1	1	1	1	1	1	1	0	Χ	8/4	3FC000H to 3FDFFFH	1FE000H to 1FEFFFH
	SA70	1	1	1	1	1	1	1	1	1	Χ	8/4	3FE000H to 3FFFFFH	1FF000H to 1FFFFFH

MBM29DL321TD Top Boot Sector Architecture

Note: The address range is A_{20} : A_{-1} if in byte mode ($\overline{BYTE} = V_{IL}$). The address range is A_{20} : A_0 if in word mode ($\overline{BYTE} = V_{IH}$).

Table 5.2 Sector Address Tables (MBM29DL321BD)

				- ;	Sec	tor	add	ress				Sector	,		
Bank	Sector		Ва	nk a							size	(×8) Address range	(×16) Address range		
		A ₂₀					A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Address range	
	SA70	1	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	3F0000H to 3FFFFFH	1F8000H to 1FFFFFH	
	SA69	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH	
	SA68	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH	
	SA67	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH	
	SA66	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH	
	SA65	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH	
	SA64	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH	
	SA63	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH	
	SA62	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH	
	SA61	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH	
	SA60	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH	
	SA59	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH	
	SA58	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH	
	SA57	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH	
	SA56	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH	
	SA55	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH	
	SA54	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH	
Bank 2	SA53	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH	
Dank 2	SA52	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH	
	SA51	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH	
	SA50	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH	
	SA49	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH	
v.DataSheet4	SA48	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH	
v.DataSneet4	SA47	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH	
	SA46	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH	
	SA45	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH	
	SA44	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH	
	SA43	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH	
	SA42	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH	
	SA41	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH	
	SA40	1	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	210000H to 21FFFFH	108000H to 10FFFFH	
	SA39	1	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	200000H to 20FFFFH	100000H to 107FFFH	
	SA38	0	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH	
	SA37	0	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH	
	SA36	0	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH	
	SA35	0	1	1	1	0	0	Χ	Χ	Х	Х	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH	

(Continued)

(Continued)

				;	Sec	tor	add	ress	3			Sector		
Bank Sector		Bank address										size	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Addic33 range	Addicas range
	SA34	0	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA33	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA32	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA31	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA30	0	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA29	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
	SA28	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
	SA27	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA26	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA25	0	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA24	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA23	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
	SA22	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	0F0000H to 0FFFFFH	078000H to 07FFFFH
Bank 2	SA21	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
	SA20	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA19	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA18	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
	SA17	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA16	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA15	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA14	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA13	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA12	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	050000H to 05FFFFH	028000H to 02FFFFH
DataSheet4l	SA11	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
	SA10	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA9	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA8	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
	SA7	0	0	0	0	0	0	1	1	1	Χ	8/4	00E000H to 00FFFFH	007000H to 007FFFH
	SA6	0	0	0	0	0	0	1	1	0	Χ	8/4	00C000H to 00DFFFH	006000H to 006FFFH
	SA5	0	0	0	0	0	0	1	0	1	Χ	8/4	00A000H to 00BFFFH	005000H to 005FFFH
Bank 1	SA4	0	0	0	0	0	0	1	0	0	Χ	8/4	008000H to 009FFFH	004000H to 004FFFH
Dailk I	SA3	0	0	0	0	0	0	0	1	1	Χ	8/4	006000H to 007FFFH	003000H to 003FFFH
	SA2	0	0	0	0	0	0	0	1	0	Χ	8/4	004000H to 005FFFH	002000H to 002FFFH
	SA1	0	0	0	0	0	0	0	0	1	Х	8/4	002000H to 003FFFH	001000H to 001FFFH
	SA0	0	0	0	0	0	0	0	0	0	Χ	8/4	000000H to 001FFFH	000000H to 000FFFH

MBM29DL321BD Bottom Boot Sector Architecture

Note: The address range is A_{20} : A_{-1} if in byte mode ($\overline{\mbox{BYTE}} = \mbox{V}_{IL}$). The address range is A_{20} : A_0 if in word mode ($\overline{\mbox{BYTE}} = \mbox{V}_{IH}$).

Table 6.1 Sector Address Tables (MBM29DL322TD)

					Sec	tor	add	ress				Sector		
Ban	k Sector	tor Bank a				Bank address						size	(×8) Address range	(×16) Address range
		A ₂₀	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Address range
	SA0	0	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	000000H to 00FFFFH	000000H to 007FFFH
	SA1	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
	SA2	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA3	0	0	0	0	1	1	Χ	Χ	Χ	Х	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA4	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
	SA5	0	0	0	1	0	1	Χ	Χ	Χ	Х	64/32	050000H to 05FFFFH	028000H to 02FFFFH
	SA6	0	0	0	1	1	0	Χ	Χ	Χ	Х	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA7	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA8	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA9	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA10	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA11	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
	SA12	0	0	1	1	0	0	Χ	Χ	Х	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA13	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA14	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
	SA15	0	0	1	1	1	1	Χ	Χ	Х	Χ	64/32	0F0000H to 0FFFFH	078000H to 07FFFFH
	SA16	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
Bank	2 SA17	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA18	0	1	0	0	1	0	Χ	Χ	Х	Х	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA19	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA20	0	1	0	1	0	0	Χ	Χ	Х	Х	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA21	0	1	0	1	0	1	Χ	Χ	Х	Х	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
www.DataShee	SA22	0	1	0	1	1	0	Χ	Χ	Χ	Х	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
	SA23	0	1	0	1	1	1	Χ	Χ	Х	Х	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA24	0	1	1	0	0	0	Χ	Χ	Х	Х	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA25	0	1	1	0	0	1	Χ	Χ	Χ	Х	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA26	0	1	1	0	1	0	Χ	Χ	Х	Х	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA27	0	1	1	0	1	1	Χ	Χ	Х	Х	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA28	0	1	1	1	0	0	Χ	Χ	Х	Х	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH
	SA29	0	1	1	1	0	1	Χ	Χ	Χ	Х	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
	SA30	0	1	1	1	1	0	Х	Х	Х	Х	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
	SA31	0	1	1	1	1	1	Χ	Χ	Х	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH
	SA32	1	0	0	0	0	0	Χ	Χ	Х	Χ	64/32	200000H to 20FFFFH	100000H to 107FFFH
	SA33	1	0	0	0	0	1	Χ	Х	Х	Х	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	SA34	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH

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				ţ	Sec	tor a	add	ress	5			Sector	(.0)	(.40)
Bank	Sector			nk a								size (Kbytes/ Kwords)	(×8) Address range	(×16) Address range
		A 20				A 16						-	_	
	SA35	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	SA36	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	SA37	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	SA38	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	SA39	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	SA40	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
	SA41	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
	SA42	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
	SA43	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	SA44	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
Bank 2	SA45	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	SA46	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
	SA47	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
	SA48	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
	SA49	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
	SA50	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	SA51	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
	SA52	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
	SA53	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	SA54	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	SA55	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	SA56	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	SA57	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
DataShe	SA58	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
	SA59	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	SA60	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH
	SA61	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	SA62	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
Bank 1	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000H to 3F1FFFH	1F8000H to 1F8FFFH
	SA64	1	1	1	1	1	1	0	0	1	Χ	8/4	3F2000H to 3F3FFFH	1F9000H to 1F9FFFH
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000H to 3F5FFFH	1FA000H to 1FAFFFH
	SA66	1	1	1	1	1	1	0	1	1	Χ	8/4	3F6000H to 3F7FFFH	1FB000H to 1FBFFFH
	SA67	1	1	1	1	1	1	1	0	0	Χ	8/4	3F8000H to 3F9FFFH	1FC000H to 1FCFFFH
	SA68	1	1	1	1	1	1	1	0	1	Χ	8/4	3FA000H to 3FBFFFH	1FD000H to 1FDFFFH
	SA69	1	1	1	1	1	1	1	1	0	Χ	8/4	3FC000H to 3FDFFFH	1FE000H to 1FEFFFH
	SA70	1	1	1	1	1	1	1	1	1	Χ	8/4	3FE000H to 3FFFFFH	1FF000H to 1FFFFFH

MBM29DL322TD Top Boot Sector Architecture

Note: The address range is A_{20} : A_{-1} if in byte mode ($\overline{BYTE} = V_{IL}$). The address range is A_{20} : A_0 if in word mode ($\overline{BYTE} = V_{IH}$).

Table 6.2 Sector Address Tables (MBM29DL322BD)

						tor a	add					Sector	,	
Bank	Sector		Ba	nk a			auu	033	•			size	(×8) Address range	(×16)
		A ₂₀		A 18			A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Addrèss range
	SA70	1	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	3F0000H to 3FFFFFH	1F8000H to 1FFFFFH
	SA69	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
	SA68	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	SA67	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH
	SA66	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	SA65	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
	SA64	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
	SA63	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	SA62	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	SA61	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	SA60	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	SA59	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
	SA58	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
	SA57	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	SA56	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
	SA55	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
	SA54	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
Donk O	SA53	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
Bank 2	SA52	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	SA51	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
	SA50	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	SA49	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
.DataSheet4	SA48	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
/.DataSHEEt4	SA47	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
	SA46	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	SA45	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	SA44	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	SA43	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	SA42	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	SA41	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH
	SA40	1	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	SA39	1	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	200000H to 20FFFFH	100000H to 107FFFH
	SA38	0	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH
	SA37	0	1	1	1	1	0	Χ	Χ	Х	Χ	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
	SA36	0	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
	SA35	0	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH

(Continued)

(Continued)

				;	Sec	tor a	add	ress	•			Sector		
Bank	Sector		Ва	nk a	ddr	ess						size (Khytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	/ tadi ooo rango	/ taul 000 rango
	SA34	0	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA33	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA32	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA31	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA30	0	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA29	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
	SA28	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
	SA27	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA26	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
Bank 2	SA25	0	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	120000H to 12FFFFH	090000H to 097FFFH
Dalik Z	SA24	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA23	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
	SA22	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	0F0000H to 0FFFFH	078000H to 07FFFFH
	SA21	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
	SA20	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA19	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA18	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
	SA17	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA16	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA15	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA14	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA13	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA12	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	050000H to 05FFFFH	028000H to 02FFFFH
ataSheet4l	SA11	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
	SA10	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA9	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA8	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
Bank 1	SA7	0	0	0	0	0	0	1	1	1	Χ	8/4	00E000H to 00FFFFH	007000H to 007FFFH
	SA6	0	0	0	0	0	0	1	1	0	Χ	8/4	00C000H to 00DFFFH	006000H to 006FFFH
	SA5	0	0	0	0	0	0	1	0	1	Χ	8/4	00A000H to 00BFFFH	005000H to 005FFFH
	SA4	0	0	0	0	0	0	1	0	0	Χ	8/4	008000H to 009FFFH	004000H to 004FFFH
	SA3	0	0	0	0	0	0	0	1	1	Χ	8/4	006000H to 007FFFH	003000H to 003FFFH
	SA2	0	0	0	0	0	0	0	1	0	Χ	8/4	004000H to 005FFFH	002000H to 002FFFH
	SA1	0	0	0	0	0	0	0	0	1	Χ	8/4	002000H to 003FFFH	001000H to 001FFFH
	SA0	0	0	0	0	0	0	0	0	0	Χ	8/4	000000H to 001FFFH	000000H to 000FFFH

MBM29DL322BD Bottom Boot Sector Architecture

Note: The address range is A_{20} : A_{-1} if in byte mode ($\overline{\mbox{BYTE}} = \mbox{V}_{IL}$). The address range is A_{20} : A_0 if in word mode ($\overline{\mbox{BYTE}} = \mbox{V}_{IH}$).

Table 7.1 Sector Address Tables (MBM29DL323TD)

					Sec							Sector	(INIDINIZ9DE3Z31D)	
Bank	Sector		Ra	nk a			auu	-	,			size	(×8)	(×16)
Dunk	ooto.	A ₂₀		A ₁₈			A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Addre `ss ´range	Addrèss range
	SA0	0	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	000000H to 00FFFFH	000000H to 007FFFH
	SA1	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
	SA2	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA3	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA4	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
	SA5	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	050000H to 05FFFFH	028000H to 02FFFFH
	SA6	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA7	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA8	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA9	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA10	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA11	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
	SA12	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA13	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA14	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
	SA15	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	0F0000H to 0FFFFH	078000H to 07FFFFH
	SA16	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
Bank 2	SA17	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA18	0	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA19	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA20	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA21	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
ataSheet4	SA22	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
	SA23	0	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA24	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA25	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA26	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA27	0	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA28	0	1	1	1	0	0	Χ	Χ	Χ	Х	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH
	SA29	0	1	1	1	0	1	Χ	Χ	Х	Х	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
	SA30	0	1	1	1	1	0	Χ	Χ	Χ	Х	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
	SA31	0	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH
	SA32	1	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	200000H to 20FFFFH	100000H to 107FFFH
	SA33	1	0	0	0	0	1	Χ	Χ	Χ	Х	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	SA34	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH

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				ţ	Sec	tor a	add	ress	5			Sector	(.O)	(.40)
Bank	Sector		Ва	nk a	ddre	ess						size (Kbytes/ Kwords)	(×8) Address range	(×16) Address range
		A ₂₀	A 19			A 16	A 15					-	_	
	SA35	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	SA36	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	SA37	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	SA38	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	SA39	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	SA40	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
Bank 2	SA41	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
	SA42	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
	SA43	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	SA44	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
	SA45	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	SA46	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
	SA47	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
	SA48	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
	SA49	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
	SA50	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	SA51	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
	SA52	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
	SA53	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	SA54	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	SA55	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	SA56	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	SA57	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
DataShe	SA58	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
Bank 1	SA59	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	SA60	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH
	SA61	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	SA62	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000H to 3F1FFFH	1F8000H to 1F8FFFH
	SA64	1	1	1	1	1	1	0	0	1	Χ	8/4	3F2000H to 3F3FFFH	1F9000H to 1F9FFFH
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000H to 3F5FFFH	1FA000H to 1FAFFFH
	SA66	1	1	1	1	1	1	0	1	1	Χ	8/4	3F6000H to 3F7FFFH	1FB000H to 1FBFFFH
	SA67	1	1	1	1	1	1	1	0	0	Χ	8/4	3F8000H to 3F9FFFH	1FC000H to 1FCFFFH
	SA68	1	1	1	1	1	1	1	0	1	Χ	8/4	3FA000H to 3FBFFFH	1FD000H to 1FDFFFH
	SA69	1	1	1	1	1	1	1	1	0	Χ	8/4	3FC000H to 3FDFFFH	1FE000H to 1FEFFFH
	SA70	1	1	1	1	1	1	1	1	1	Χ	8/4	3FE000H to 3FFFFFH	1FF000H to 1FFFFFH

MBM29DL323TD Top Boot Sector Architecture

Note: The address range is A_{20} : A_{-1} if in byte mode ($\overline{BYTE} = V_{IL}$). The address range is A_{20} : A_0 if in word mode ($\overline{BYTE} = V_{IH}$).

Table 7.2 Sector Address Tables (MBM29DL323BD)

					- ;	Sec	tor a	add	ress				Sector	,	
Baı	nk Se	ector		Ва	nk a					-			size	(×8) Address range	(×16) Address range
		ŧ	A ₂₀		A 18			A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Address range
	S	A70	1	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	3F0000H to 3FFFFFH	1F8000H to 1FFFFFH
	S	A69	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
	S	A68	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	S	A67	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH
	S	A66	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	S	A65	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
	S	A64	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
	S	A63	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	S	A62	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	S	A61	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	S	A60	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	S	A59	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
	S	A58	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
	S	A57	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	S	A56	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
	S	A55	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
	S	A54	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
Ban	S.	A53	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
Dan	S.	A52	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	S	A51	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
	S	A50	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	S	A49	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
/.DataShe	S	A48	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
7.DataSire	S	A47	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
	S	A46	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	S	A45	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	S	A44	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	S	A43	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	S	A42	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	S	A41	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH
	S	A40	1	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	S	A39	1	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	200000H to 20FFFFH	100000H to 107FFFH
	S	A38	0	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH
	S	A37	0	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
	S	A36	0	1	1	1	0	1	Χ	Χ	Χ	Х	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
		A35	0	1	1	1	0	0	Χ	Χ	Χ	Х	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH

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(Continued)

				;	Sec	tor a	add	ress	5			Sector		
Bank	Sector		Ва	nk a	ddre	ess						size (Kbvtes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13		A 11	(Kbytes/ Kwords)		
	SA34	0	1	1	0	1	1	X	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA33	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA32	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA31	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA30	0	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
Bank 2	SA29	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
Darik Z	SA28	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
	SA27	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA26	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA25	0	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA24	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA23	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
	SA22	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	0F0000H to 0FFFFH	078000H to 07FFFFH
	SA21	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
	SA20	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA19	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA18	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
	SA17	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA16	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA15	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA14	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA13	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA12	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	050000H to 05FFFFH	028000H to 02FFFFH
Bank 14	SA11	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
	SA10	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA9	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA8	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
	SA7	0	0	0	0	0	0	1	1	1	Χ	8/4	00E000H to 00FFFFH	007000H to 007FFFH
	SA6	0	0	0	0	0	0	1	1	0	Χ	8/4	00C000H to 00DFFFH	006000H to 006FFFH
	SA5	0	0	0	0	0	0	1	0	1	Χ	8/4	00A000H to 00BFFFH	005000H to 005FFFH
	SA4	0	0	0	0	0	0	1	0	0	Χ	8/4	008000H to 009FFFH	004000H to 004FFFH
	SA3	0	0	0	0	0	0	0	1	1	Χ	8/4	006000H to 007FFFH	003000H to 003FFFH
	SA2	0	0	0	0	0	0	0	1	0	Χ	8/4	004000H to 005FFFH	002000H to 002FFFH
	SA1	0	0	0	0	0	0	0	0	1	Χ	8/4	002000H to 003FFFH	001000H to 001FFFH
	SA0	0	0	0	0	0	0	0	0	0	Χ	8/4	000000H to 001FFFH	000000H to 000FFFH

MBM29DL323BD Bottom Boot Sector Architecture

Note: The address range is A₂₀: A₋₁ if in byte mode ($\overline{\text{BYTE}} = \text{V}_{\text{IL}}$). The address range is A₂₀: A₀ if in word mode ($\overline{\text{BYTE}} = \text{V}_{\text{IH}}$).

Table 8.1 Sector Address Tables (MBM29DL324TD)

					Sec	tor :	add	ress				Sector		
Bank	Sector		Ba	nk a			uuu		_			Size	(×8)	(×16) Address range
		A ₂₀			A 17		A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Address range
	SA0	0	0	0	0	0	0	Χ	Χ	Χ	Χ	64/32	000000H to 00FFFFH	000000H to 007FFFH
	SA1	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
	SA2	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA3	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA4	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
	SA5	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	050000H to 05FFFFH	028000H to 02FFFFH
	SA6	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA7	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA8	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA9	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA10	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA11	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
	SA12	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA13	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA14	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
Donle	SA15	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	0F0000H to 0FFFFH	078000H to 07FFFFH
Bank	SA16	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
	SA17	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA18	0	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA19	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA20	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA21	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
DataShee	SA22	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
DataSnee	SA23	0	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA24	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA25	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA26	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA27	0	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA28	0	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH
	SA29	0	1	1	1	0	1	Χ	Χ	Х	Χ	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
	SA30	0	1	1	1	1	0	Χ	Χ	Х	Χ	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
	SA31	0	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFH
	SA32	1	0	0	0	0	0	Χ	Χ	Х	Χ	64/32	200000H to 20FFFFH	100000H to 107FFFH
Bank	1 SA33	1	0	0	0	0	1	Χ	Χ	Х	Χ	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	SA34	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH

(Continued)

(Continued)

				;	Sec	tor a	add	ress	•			Sector	(0)	(40)
Bank	Sector		Ва	nk a	ddre	ess						size (Kbytes/ Kwords)	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15					-	_	
	SA35	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	SA36	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	SA37	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	SA38	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	SA39	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	SA40	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
	SA41	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
	SA42	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
	SA43	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	SA44	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
	SA45	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	SA46	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
	SA47	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
	SA48	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
	SA49	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
	SA50	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	SA51	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
Donk 1	SA52	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
Bank 1	SA53	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	SA54	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	SA55	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	SA56	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	SA57	1	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
DataShe	SA58	1	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
	SA59	1	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	SA60	1	1	1	1	0	0	Χ	Χ	Χ	Χ	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFFH
	SA61	1	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	SA62	1	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000H to 3F1FFFH	1F8000H to 1F8FFFH
	SA64	1	1	1	1	1	1	0	0	1	Χ	8/4	3F2000H to 3F3FFFH	1F9000H to 1F9FFFH
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000H to 3F5FFFH	1FA000H to 1FAFFFH
	SA66	1	1	1	1	1	1	0	1	1	Χ	8/4	3F6000H to 3F7FFFH	1FB000H to 1FBFFFH
	SA67	1	1	1	1	1	1	1	0	0	Χ	8/4	3F8000H to 3F9FFFH	1FC000H to 1FCFFFH
	SA68	1	1	1	1	1	1	1	0	1	Χ	8/4	3FA000H to 3FBFFFH	1FD000H to 1FDFFFH
	SA69	1	1	1	1	1	1	1	1	0	Χ	8/4	3FC000H to 3FDFFFH	1FE000H to 1FEFFFH
	SA70	1	1	1	1	1	1	1	1	1	Χ	8/4	3FE000H to 3FFFFFH	1FF000H to 1FFFFFH

MBM29DL324TD Top Boot Sector Architecture

Note: The address range is A_{20} : A_{-1} if in byte mode ($\overline{BYTE} = V_{IL}$). The address range is A_{20} : A_0 if in word mode ($\overline{BYTE} = V_{IH}$).

Table 8.2 Sector Address Tables (MBM29DL324BD)

										Auc	41 00	Т	(MIDIMIZSDESZ4DD)	
			_			tor a	add	ress	3			Sector size	(×8)	(×16)
Bank	Sector			nk a								(Kbytes/	Address range	(×16) Address range
	C A 70					A 16						64/32	250000H to 25555H	1F8000H to 1FFFFFH
	SA70	1	1	1	1	1	1	X	X	X	X		3F0000H to 3FFFFFH	
	SA69	1	1	1	1	1	0	X	X	X	X	64/32	3E0000H to 3EFFFFH	1F0000H to 1F7FFFH
	SA68	1	1	1	1	0	1	X	X	X	X	64/32	3D0000H to 3DFFFFH	1E8000H to 1EFFFFH
	SA67	1	1	1	1	0	0	X	X	X	X	64/32	3C0000H to 3CFFFFH	1E0000H to 1E7FFH
	SA66	1	1	1	0	1	1	X	X	X	X	64/32	3B0000H to 3BFFFFH	1D8000H to 1DFFFFH
	SA65	1	1	1	0	1	0	X	Х	X	X	64/32	3A0000H to 3AFFFFH	1D0000H to 1D7FFFH
	SA64	1	1	1	0	0	1	Χ	Х	Х	Х	64/32	390000H to 39FFFFH	1C8000H to 1CFFFFH
	SA63	1	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	380000H to 38FFFFH	1C0000H to 1C7FFFH
	SA62	1	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	370000H to 37FFFFH	1B8000H to 1BFFFFH
	SA61	1	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	360000H to 36FFFFH	1B0000H to 1B7FFFH
	SA60	1	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	350000H to 35FFFFH	1A8000H to 1AFFFFH
	SA59	1	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	340000H to 34FFFFH	1A0000H to 1A7FFFH
	SA58	1	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	330000H to 33FFFFH	198000H to 19FFFFH
	SA57	1	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	320000H to 32FFFFH	190000H to 197FFFH
	SA56	1	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	310000H to 31FFFFH	188000H to 18FFFFH
Bank 2	SA55	1	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	300000H to 30FFFFH	180000H to 187FFFH
Dalik 2	SA54	1	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	2F0000H to 2FFFFFH	178000H to 17FFFFH
	SA53	1	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	2E0000H to 2EFFFFH	170000H to 177FFFH
	SA52	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000H to 2DFFFFH	168000H to 16FFFFH
	SA51	1	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	2C0000H to 2CFFFFH	160000H to 167FFFH
	SA50	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000H to 2BFFFFH	158000H to 15FFFFH
	SA49	1	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	2A0000H to 2AFFFFH	150000H to 157FFFH
vw.DataSheet4	SA48	1	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	290000H to 29FFFFH	148000H to 14FFFFH
vw.DataSHEEt4	SA47	1	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	280000H to 28FFFFH	140000H to 147FFFH
	SA46	1	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	270000H to 27FFFFH	138000H to 13FFFFH
	SA45	1	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	260000H to 26FFFFH	130000H to 137FFFH
	SA44	1	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	250000H to 25FFFFH	128000H to 12FFFFH
	SA43	1	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	240000H to 24FFFFH	120000H to 127FFFH
	SA42	1	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	230000H to 23FFFFH	118000H to 11FFFFH
	SA41	1	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	220000H to 22FFFFH	110000H to 117FFFH
	SA40	1	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	210000H to 21FFFFH	108000H to 10FFFFH
	SA39	1	0	0	0	0	0	Χ	Χ	Χ	Х	64/32	200000H to 20FFFFH	100000H to 107FFFH
	SA38	0	1	1	1	1	1	Χ	Χ	Χ	Χ	64/32	1F0000H to 1FFFFFH	0F8000H to 0FFFFFH
	SA37	0	1	1	1	1	0	X	X	X	X	64/32	1E0000H to 1EFFFFH	0F0000H to 0F7FFFH
Bank 1	SA36	0	1	1	1	0	1	X	X	Х	Х	64/32	1D0000H to 1DFFFFH	0E8000H to 0EFFFFH
	SA35	0	1	1	1	0	0	X	X	X	X	64/32	1C0000H to 1CFFFFH	0E0000H to 0E7FFFH
	5,155	٥		'	•	٥)	^\	^	^	^	0-7/02	1000001110 101111111	0_00001110 0E711111

(Continued)

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Ò				;	Sec	tor	add	ress	S			Sector	(0)	
Bank	Sector		Ва	nk a	ddre	ess						size (Kbytes/ Kwords)	(×8) Address range	(×16) Address range
		A ₂₀	A 19	A 18	A 17	A 16	A 15					-		
	SA34	0	1	1	0	1	1	Χ	Χ	Χ	Χ	64/32	1B0000H to 1BFFFFH	0D8000H to 0DFFFFH
	SA33	0	1	1	0	1	0	Χ	Χ	Χ	Χ	64/32	1A0000H to 1AFFFFH	0D0000H to 0D7FFFH
	SA32	0	1	1	0	0	1	Χ	Χ	Χ	Χ	64/32	190000H to 19FFFFH	0C8000H to 0CFFFFH
	SA31	0	1	1	0	0	0	Χ	Χ	Χ	Χ	64/32	180000H to 18FFFFH	0C0000H to 0C7FFFH
	SA30	0	1	0	1	1	1	Χ	Χ	Χ	Χ	64/32	170000H to 17FFFFH	0B8000H to 0BFFFFH
	SA29	0	1	0	1	1	0	Χ	Χ	Χ	Χ	64/32	160000H to 16FFFFH	0B0000H to 0B7FFFH
	SA28	0	1	0	1	0	1	Χ	Χ	Χ	Χ	64/32	150000H to 15FFFFH	0A8000H to 0AFFFFH
	SA27	0	1	0	1	0	0	Χ	Χ	Χ	Χ	64/32	140000H to 14FFFFH	0A0000H to 0A7FFFH
	SA26	0	1	0	0	1	1	Χ	Χ	Χ	Χ	64/32	130000H to 13FFFFH	098000H to 09FFFFH
	SA25	0	1	0	0	1	0	Χ	Χ	Χ	Χ	64/32	120000H to 12FFFFH	090000H to 097FFFH
	SA24	0	1	0	0	0	1	Χ	Χ	Χ	Χ	64/32	110000H to 11FFFFH	088000H to 08FFFFH
	SA23	0	1	0	0	0	0	Χ	Χ	Χ	Χ	64/32	100000H to 10FFFFH	080000H to 087FFFH
	SA22	0	0	1	1	1	1	Χ	Χ	Χ	Χ	64/32	0F0000H to 0FFFFFH	078000H to 07FFFFH
	SA21	0	0	1	1	1	0	Χ	Χ	Χ	Χ	64/32	0E0000H to 0EFFFFH	070000H to 077FFFH
	SA20	0	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	0D0000H to 0DFFFFH	068000H to 06FFFFH
	SA19	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000H to 0CFFFFH	060000H to 067FFFH
	SA18	0	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	0B0000H to 0BFFFFH	058000H to 05FFFFH
Bank 1	SA17	0	0	1	0	1	0	Χ	Χ	Χ	Χ	64/32	0A0000H to 0AFFFFH	050000H to 057FFFH
	SA16	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000H to 09FFFFH	048000H to 04FFFFH
	SA15	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000H to 08FFFFH	040000H to 047FFFH
	SA14	0	0	0	1	1	1	Χ	Χ	Χ	Χ	64/32	070000H to 07FFFFH	038000H to 03FFFFH
	SA13	0	0	0	1	1	0	Χ	Χ	Χ	Χ	64/32	060000H to 06FFFFH	030000H to 037FFFH
	SA12	0	0	0	1	0	1	Χ	Χ	Χ	Χ	64/32	050000H to 05FFFFH	028000H to 02FFFFH
.DataSheet4	SA11	0	0	0	1	0	0	Χ	Χ	Χ	Χ	64/32	040000H to 04FFFFH	020000H to 027FFFH
7.DataSneet4	SA10	0	0	0	0	1	1	Χ	Χ	Χ	Χ	64/32	030000H to 03FFFFH	018000H to 01FFFFH
	SA9	0	0	0	0	1	0	Χ	Χ	Χ	Χ	64/32	020000H to 02FFFFH	010000H to 017FFFH
	SA8	0	0	0	0	0	1	Χ	Χ	Χ	Χ	64/32	010000H to 01FFFFH	008000H to 00FFFFH
	SA7	0	0	0	0	0	0	1	1	1	Χ	8/4	00E000H to 00FFFFH	007000H to 007FFFH
	SA6	0	0	0	0	0	0	1	1	0	Χ	8/4	00C000H to 00DFFFH	006000H to 006FFFH
	SA5	0	0	0	0	0	0	1	0	1	Χ	8/4	00A000H to 00BFFFH	005000H to 005FFFH
	SA4	0	0	0	0	0	0	1	0	0	Χ	8/4	008000H to 009FFFH	004000H to 004FFFH
	SA3	0	0	0	0	0	0	0	1	1	Х	8/4	006000H to 007FFFH	003000H to 003FFFH
	SA2	0	0	0	0	0	0	0	1	0	Х	8/4	004000H to 005FFFH	002000H to 002FFFH
	SA1	0	0	0	0	0	0	0	0	1	Х	8/4	002000H to 003FFFH	001000H to 001FFFH
	SA0	0	0	0	0	0	0	0	0	0	Х	8/4	000000H to 001FFFH	000000H to 000FFFH
	J, 10	J	,	J	J	J	J	J	,	,	<i>^</i> \	5 / ∓	2200001110	2200001110

MBM29DL324BD Bottom Boot Sector Architecture

Note: The address range is A₂₀: A₋₁ if in byte mode ($\overline{\text{BYTE}} = \text{V}_{\text{IL}}$). The address range is A₂₀: A₀ if in word mode ($\overline{\text{BYTE}} = \text{V}_{\text{IH}}$).

Table 9.1 Sector Group Addresses (MBM29DL32XTD) (Top Boot Block)

Sector group	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	Sectors
SGA0	0	0	0	0	0	0	Х	Х	Х	SA0
					0	1				
SGA1	0	0	0	0	1	0	Х	X	X	SA1 to SA3
					1	1	1			
SGA2	0	0	0	1	Х	Х	Х	Х	Х	SA4 to SA7
SGA3	0	0	1	0	Х	Х	Х	Х	Х	SA8 to SA11
SGA4	0	0	1	1	Х	Х	Х	Х	Х	SA12 to SA15
SGA5	0	1	0	0	Х	Х	Х	Х	Х	SA16 to SA19
SGA6	0	1	0	1	Х	Х	Х	Х	Х	SA20 to SA23
SGA7	0	1	1	0	Х	Х	Х	Х	Х	SA24 to SA27
SGA8	0	1	1	1	Х	Х	Х	Х	Х	SA28 to SA31
SGA9	1	0	0	0	Х	Х	Х	Х	Х	SA32 to SA35
SGA10	1	0	0	1	Х	Х	Х	Х	Х	SA36 to SA39
SGA11	1	0	1	0	Х	Х	Х	Х	Х	SA40 to SA43
SGA12	1	0	1	1	Х	Х	Х	Х	Х	SA44 to SA47
SGA13	1	1	0	0	Х	Х	Х	Х	Х	SA48 to SA51
SGA14	1	1	0	1	Х	Х	Х	Х	Х	SA52 to SA55
SGA15	1	1	1	0	Х	Х	Х	Х	Х	SA56 to SA59
					0	0				
D a SGA16 е е	1	1	1	1	0	1	Х	X	X	SA60 to SA62
					1	0				
SGA17	1	1	1	1	1	1	0	0	0	SA63
SGA18	1	1	1	1	1	1	0	0	1	SA64
SGA19	1	1	1	1	1	1	0	1	0	SA65
SGA20	1	1	1	1	1	1	0	1	1	SA66
SGA21	1	1	1	1	1	1	1	0	0	SA67
SGA22	1	1	1	1	1	1	1	0	1	SA68
SGA23	1	1	1	1	1	1	1	1	0	SA69
SGA24	1	1	1	1	1	1	1	1	1	SA70

w w w

Table 9.2 Sector Group Addresses (MBM29DL32XBD) (Bottom Boot Block)

Sector group	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	Sectors
SGA0	0	0	0	0	0	0	0	0	0	SA0
SGA1	0	0	0	0	0	0	0	0	1	SA1
SGA2	0	0	0	0	0	0	0	1	0	SA2
SGA3	0	0	0	0	0	0	0	1	1	SA3
SGA4	0	0	0	0	0	0	1	0	0	SA4
SGA5	0	0	0	0	0	0	1	0	1	SA5
SGA6	0	0	0	0	0	0	1	1	0	SA6
SGA7	0	0	0	0	0	0	1	1	1	SA7
					0	1				
SGA8	0	0	0	0	1	0	Х	Х	Χ	SA8 to SA10
					1	1	1			
SGA9	0	0	0	1	Х	Х	Х	Х	Χ	SA11 to SA14
SGA10	0	0	1	0	Х	Х	Х	Х	Χ	SA15 to SA18
SGA11	0	0	1	1	Х	Х	Х	Х	Χ	SA19 to SA22
SGA12	0	1	0	0	Х	Х	Х	Χ	Χ	SA23 to SA26
SGA13	0	1	0	1	Х	Х	Х	Х	Χ	SA27 to SA30
SGA14	0	1	1	0	Х	Х	Х	Х	Χ	SA31 to SA34
SGA15	0	1	1	1	Х	Х	Х	Χ	Χ	SA35 to SA38
SGA16	1	0	0	0	Х	Х	Х	Х	Χ	SA39 to SA42
D a SGA17 e e	1	0	0	1	Х	Х	Х	Х	Х	SA43 to SA46
SGA18	1	0	1	0	Х	Х	Х	Χ	Χ	SA47 to SA50
SGA19	1	0	1	1	Х	Х	Х	Χ	Χ	SA51 to SA54
SGA20	1	1	0	0	Х	Х	Х	Х	Χ	SA55 to SA58
SGA21	1	1	0	1	Х	Х	Х	Х	Χ	SA59 to SA62
SGA22	1	1	1	0	Х	Х	Х	Х	Χ	SA63 to SA66
					0	0				
SGA23	1	1	1	1	0	1	Х	Х	Χ	SA67 to SA69
					1	0	1			
SGA24	1	1	1	1	1	1	Х	Х	Х	SA70

w w w

■ FUNCTIONAL DESCRIPTION

Simultaneous Operation

MBM29DL32XTD/BD have feature, which is capability of reading data from one bank of memory while a program or erase operation is in progress in the other bank of memory (simultaneous operation), in addition to the conventional features (read, program, erase, erase-suspend read, and erase-suspend program). The bank selection can be selected by bank address (A₁₅ to A₂₀) with zero latency.

The MBM29DL321TD/BD have two banks which contain

Bank 1 (8KB × eight sectors) and Bank 2 (64KB × sixty-three sectors).

The MBM29DL322TD/BD have two banks which contain

Bank 1 (8KB × eight sectors, 64KB × seven sectors) and Bank 2 (64KB × fifty-six sectors).

The MBM29DL323TD/BD have two banks which contain

Bank 1 (8KB × eight sectors, 64KB × fifteen sectors) and Bank 2 (64KB × forty-eight sectors).

The MBM29DL324TD/BD have two banks which contain

Bank 1 (8KB \times eight sectors, 64KB \times thirty-one sectors) and Bank 2 (64KB \times thirty-two sectors).

The simultaneous operation can not execute multi-function mode in the same bank. Table 10 shows combination to be possible for simultaneous operation. (Refer to the Figure 11 Back-to-back Read/Write Timing Diagram.)

	Case	Bank 1 status	Bank 2 status
	1	Read Mode	Read Mode
	2	Read Mode	Autoselect Mode
	3	Read Mode	Program Mode
	4	Read Mode	Erase Mode *
	5	Autoselect Mode	Read Mode
www.Da	rtaSheet4U.com 6	Program Mode	Read Mode
	7	Erase Mode *	Read Mode

Table 10 Simultaneous Operation

Read Mode

The MBM29DL32XTD/BD have two control functions which must be satisfied in order to obtain data at the outputs. $\overline{\text{CE}}$ is the power control and should be used for a device selection. $\overline{\text{OE}}$ is the output control and should be used to gate data to the output pins if a device is selected.

Address access time (tacc) is equal to the delay from stable addresses to valid output data. The chip enable access time (tce) is the delay from stable addresses and stable \overline{CE} to valid data at the output pins. The output enable access time is the delay from the falling edge of \overline{OE} to valid data at the output pins. (Assuming the addresses have been stable for at least tacc-toe time.) When reading out a data without changing addresses after power-up, it is necessary to input hardware reset or to change \overline{CE} pin from "H" or "L"

^{*:} An erase operation may also be supended to read from or program to a sector not being erased.

Standby Mode

There are two ways to implement the standby mode on the MBM29DL32XTD/BD devices, one using both the $\overline{\text{CE}}$ and $\overline{\text{RESET}}$ pins; the other via the $\overline{\text{RESET}}$ pin only.

When using both pins, a CMOS standby mode is achieved with $\overline{\text{CE}}$ and $\overline{\text{RESET}}$ inputs both held at $V\text{cc} \pm 0.3 \text{ V}$. Under this condition the current consumed is less than 5 μA max. During Embedded Algorithm operation, Vcc active current (Icc2) is required even $\overline{\text{CE}}$ = "H". The device can be read with standard access time (Icc5) from either of these standby modes.

When using the $\overline{\text{RESET}}$ pin only, a CMOS standby mode is achieved with $\overline{\text{RESET}}$ input held at Vss \pm 0.3 V ($\overline{\text{CE}}$ = "H" or "L"). Under this condition the current is consumed is less than 5 μ A max. Once the $\overline{\text{RESET}}$ pin is taken high, the device requires tree of wake up time before outputs are valid for read access.

In the standby mode the outputs are in the high impedance state, independent of the $\overline{\text{OE}}$ input.

Automatic Sleep Mode

There is a function called automatic sleep mode to restrain power consumption during read-out of MBM29DL32XTD/BD data. This mode can be used effectively with an application requested low power consumption such as handy terminals.

To activate this mode, MBM29DL32XTD/BD automatically switch themselves to low power mode when MBM29DL32XTD/BD addresses remain stably during access fine of 150 ns. It is not necessary to control $\overline{\text{CE}}$, $\overline{\text{WE}}$, and $\overline{\text{OE}}$ on the mode. Under the mode, the current consumed is typically 1 μA (CMOS Level).

During simultaneous operation, Vcc active current (Icc2) is required.

Since the data are latched during this mode, the data are read-out continuously. If the addresses are changed, the mode is canceled automatically and MBM29DL32XTD/BD read-out the data for changed addresses.

Output Disable

With the $\overline{\text{OE}}$ input at a logic high level (V_{IH}), output from the devices are disabled. This will cause the output pins www.DataStotoEincarhigh impedance state.

Autoselect

The autoselect mode allows the reading out of a binary code from the devices and will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the devices to be programmed with its corresponding programming algorithm. This mode is functional over the entire temperature range of the devices.

To activate this mode, the programming equipment must force V_{ID} (11.5 V to 12.5 V) on address pin A_9 . Two identifier bytes may then be sequenced from the devices outputs by toggling address A_0 from V_{IL} to V_{IH} . All addresses are DON'T CARES except A_0 , A_1 , and A_6 (A_{-1}). (See Tables 3 and 4.)

The manufacturer and device codes may also be read via the command register, for instances when the MBM29DL32XTD/BD are erased or programmed in a system without access to high voltage on the A₉ pin. The command sequence is illustrated in Table 12. (Refer to Autoselect Command section.)

Byte 0 ($A_0 = V_{IL}$) represents the manufacturer's code (Fujitsu = 04H) and word 1 ($A_0 = V_{IH}$) represents the device identifier code (MBM29DL321TD = 59H and MBM29DL321BD = 5AH for ×8 mode; MBM29DL321TD = 2259H and MBM29DL321BD = 225AH for ×16 mode). (MBM29DL322TD = 55H and MBM29DL322BD = 56H for ×8 mode; MBM29DL322TD = 2255H and MBM29DL322BD = 2256H for ×16 mode). (MBM29DL323TD = 50H and MBM29DL323BD = 53H for ×8 mode; MBM29DL323TD = 2250H and MBM29DL323BD = 2253H for ×16 mode). (MBM29DL324TD = 5CH and MBM29DL324BD = 5FH for ×8 mode; MBM29DL324TD = 225CH and MBM29DL324BD = 225FH for ×16 mode). These two bytes/words are given in the tables 11.1 to 11.8. All identifiers for manufactures and device will exhibit odd parity with DQ7 defined as the parity bit. In order to read the proper device codes when executing the autoselect, A1 must be V_{IL} . (See Tables 11.1 to 11.8.)

In case of applying V_{ID} on A_9 , since both Bank 1 and Bank 2 enters Autoselect mode, the simultenous operation can not be executed.

				•		•		
	Туре		A ₁₂ to A ₂₀	A 6	A 1	Ao	A -1*1	Code (HEX)
Manufa	cture's Code		Х	VIL	Vıl	VıL	VIL	04H
	MBM29DL321TD	Byte	Х	VIL	VIL	Vih	VIL	59H
Device	MBMZ9DL3Z11D	Word	^	VIL	VIL	VIH	Х	2259H
Code	MBM29DL321BD	Byte	Х	VIL	VIL	Vih	VIL	5AH
	MIDINIZADE25 I PD	Word	^	VIL	VIL	VIH	Х	225AH
Sector	Group Protection		Sector Group Addresses	VIL	VIH	VıL	VIL	01H*2

Table 11.1 MBM29DL321TD/BD Sector Group Protection Verify Autoselect Codes

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Table 11.2 Expanded Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ ₁₀	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ₅	DQ ₄	DQ ₃	DQ ₂	DQ ₁	DQo
Manufa	cturer's Code		04H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
	MBM29DL321TD			A -1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	1	0	0	1
Device	Device	(W)	2259H	0	0	1	0	0	0	1	0	0	1	0	1	1	0	0	1
Code	MPM20DI 221PD	(B)	5AH	A -1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	1	0	1	0
	MBM29DL321BD		225AH	0	0	1	0	0	0	1	0	0	1	0	1	1	0	1	0
Sector	Sector Group Protection		01H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

(B): Byte mode (W): Word mode

^{*1:} A-1 is for Byte mode.

^{*2:} Outputs 01H at protected sector group addresses and outputs 00H at unprotected sector group addresses.

Table 11.3 MBM29DL322TD/BD Sector Group Protection Verify Autoselect Codes

	Туре		A ₁₂ to A ₂₀	A 6	A 1	Αo	A -1*1	Code (HEX)
Manufa	cture's Code		Х	Vıl	VIL	Vıl	VIL	04H
	MBM29DL322TD	Byte	X	VIL	VIL	Vih	VIL	55H
Device	WIBINIZ 9DL 322 I D	Word	^	VIL	VIL	VIH	Χ	2255H
Code	MBM29DL322BD	Byte	Х	VIL	VIL	VIH	VIL	56H
	INIDINI29DL322DD	Word	^	VIL	VIL	VIH	Х	2256H
Sector	Group Protection		Sector group addresses	VIL	ViH	VıL	VIL	01H*2

^{*1:} A-1 is for Byte mode.

Table 11.4 Expanded Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ ₁₀	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ ₅	DQ ₄	DQ ₃	DQ ₂	DQ₁	DQ₀
Manufa	cturer's Code		04H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
			55H	A-1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	1	0	1
Device		(W)	2255H	0	0	1	0	0	0	1	0	0	1	0	1	0	1	0	1
Code	MPM20DI 222PD	(B)	56H	A -1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0 1 0 1 0 0 1 0 1 0 0 1 0 1 1 0 1 0 1 1		0			
	MBM29DL322BD		2256H	0	0	1	0	0	0	1	0	0	1	0	1	0	1	1	0
Sector	Sector Group Protection		01H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

www. [(B): Bytesmode (W): Word mode

^{*2:} Outputs 01H at protected sector group addresses and outputs 00H at unprotected sector group addresses.

Table 11.5 MBM29DL323TD/BD Sector Group Protection Verify Autoselect Codes

	Туре		A ₁₂ to A ₂₀	A 6	A 1	Ao	A -1*1	Code (HEX)
Manufa	cture's Code		Х	VIL	Vıl	VIL	VıL	04H
	MBM29DL323TD	Byte	Х	V.	Mi	Mari	VIL	50H
Device	WIBINI29DL3231D	Word	^	Vıl	Vıl	Vін	Х	2250H
Code	MBM29DL323BD	Byte	Х	V.	VIL	V	VIL	53H
	MIDIMIZADE222DD	Word	^	Vıl	VIL	Vін	Х	2253H
Sector (Group Protection		Sector group addresses	VIL	Vıн	VıL	VıL	01H*2

^{*1:} A-1 is for Byte mode.

Table 11.6 Expanded Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ ₁₀	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ₅	DQ ₄	DQ₃	DQ ₂	DQ₁	DQ ₀
Manufa	cturer's Code		04H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
	MBM29DL323TD		50H	A-1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	0	0	0
Device	vice		2250H	0	0	1	0	0	0	1	0	0	1	0	1	0	0	0	0
Code	MPM20DI 222DD	(B)	53H	A-1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	0	1	1
	MBM29DL323BD		2253H	0	0	1	0	0	0	1	0	0	1	0	1	0	0	1	1
Sector	Sector Group Protection		01H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

www. [(B): Bytesmode (W): Word mode

^{*2:} Outputs 01H at protected sector group addresses and outputs 00H at unprotected sector group addresses.

Table 11.7 MBM29DL324TD/BD Sector Group Protection Verify Autoselect Codes

	Туре		A ₁₂ to A ₂₀	A 6	A 1	Ao	A -1*1	Code (HEX)
Manufa	cture's Code		Х	VIL	Vıl	VIL	Vıl	04H
	MBM29DL324TD	Byte	Х	VIL	VIL	Vih	Vıl	5CH
Device	WIBINI29DL3241D	Word	^	VIL	VIL	VIH	Х	225CH
Code	MBM29DL324BD	Byte	V	V.	M	V	VIL	5FH
	WIDINI29DL324BD	Word	X	Vıl	Vıl	ViH	Х	225FH
Sector (Group Protection		Sector group addresses	VıL	ViH	VıL	VIL	01H*2

^{*1:} A-1 is for Byte mode.

Table 11.8 Expanded Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ ₁₀	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ ₅	DQ ₄	DQ ₃	DQ ₂	DQ ₁	DQ₀
Manufa	cturer's Code		04H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
	MBM29DL324TD	(B)	5CH	A -1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	1	1	0	0
Device	IVIDIVIZ9DL3241D	(W)	225CH	0	0	1	0	0	0	1	0	0	1	0	1	1	1	0	0
Code	MBM20DI 224BD	(B)	5FH	A -1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	1	1	1	1
	MBM29DL324BD		225FH	0	0	1	0	0	0	1	0	0	1	0	1	1	1	1	1
Sector	Group Protection		01H	A-1/0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

www. [(B): Bytesmode (W): Word mode

^{*2:} Outputs 01H at protected sector group addresses and outputs 00H at unprotected sector group addresses.

Write

Device erasure and programming are accomplished via the command register. The contents of the register serve as inputs to the internal state machine. The state machine outputs dictate the function of the device.

The command register itself does not occupy any addressable memory location. The register is a latch used to store the commands, along with the address and data information needed to execute the command. The command register is written by bringing \overline{WE} to V_{IL} , while \overline{CE} is at V_{IL} and \overline{OE} is at V_{IH} . Addresses are latched on the falling edge of \overline{WE} or \overline{CE} , whichever happens later; while data is latched on the rising edge of \overline{WE} or \overline{CE} , whichever happens first. Standard microprocessor write timings are used.

Refer to AC Write Characteristics and the Erase/Programming Waveforms for specific timing parameters.

Sector Group Protection

The MBM29DL32XTD/BD feature hardware sector group protection. This feature will disable both program and erase operations in any combination of twenty five sector groups of memory. (See Tables 9.1 and 9.2). The sector group protection feature is enabled using programming equipment at the user's site. The device is shipped with all sector groups unprotected.

To activate this mode, the programming equipment must force V_{ID} on address pin A_9 and control pin \overline{OE} , (suggest $V_{ID} = 11.5 \text{ V}$), $\overline{CE} = V_{IL}$ and $A_0 = A_6 = V_{IL}$, $A_1 = V_{IH}$. The sector group addresses (A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{15} , A_{14} , A_{13} , and A_{12}) should be set to the sector to be protected. Tables 5.1 to 8.2 define the sector address for each of the seventy one (71) individual sectors, and tables 9.1 and 9.2 define the sector group address for each of the twenty five (25) individual group sectors. Programming of the protection circuitry begins on the falling edge of the \overline{WE} pulse and is terminated with the rising edge of the same. Sector group addresses must be held constant during the \overline{WE} pulse. See Figures 18 and 26 for sector group protection waveforms and algorithm.

To verify programming of the protection circuitry, the programming equipment must force V_{ID} on address pin A_9 with \overline{CE} and \overline{OE} at V_{IL} and \overline{WE} at V_{IH} . Scanning the sector group addresses (A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{15} , A_{14} , A_{13} , and A_{12}) while (A_6 , A_1 , A_0) = (0, 1, 0) will produce a logical "1" code at device output DQ $_0$ for a protected sector. Otherwise the device will produce "0" for unprotected sector. In this mode, the lower order addresses, except for A_0 , A_1 , and A_6 are DON'T CARES. Address locations with $A_1 = V_{IL}$ are reserved for Autoselect manufacturer and device codes. A_{-1} requires to apply to V_{IL} on byte mode.

It is also possible to determine if a sector group is protected in the system by writing an Autoselect command. Performing a read operation at the address location XX02H, where the higher order addresses (A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{14} , A_{13} , and A_{12}) are the desired sector group address will produce a logical "1" at DQ₀ for a protected sector group. See Tables 11.1 to 11.8 for Autoselect codes.

Temporary Sector Group Unprotection

This feature allows temporary unprotection of previously protected sector groups of the MBM29DL32XTD/BD devices in order to change data. The Sector Group Unprotection mode is activated by setting the \overline{RESET} pin to high voltage (V_{ID}). During this mode, formerly protected sector groups can be programmed or erased by selecting the sector group addresses. Once the V_{ID} is taken away from the \overline{RESET} pin, all the previously protected sector groups will be protected again. Refer to Figures 19 and 27.

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RESET

Hardware Reset

The MBM29DL32XTD/BD devices may be reset by driving the \overline{RESET} pin to V_{IL} . The \overline{RESET} pin has a pulse requirement and has to be kept low (V_{IL}) for at least " t_{RP} " in order to properly reset the internal state machine. Any operation in the process of being executed will be terminated and the internal state machine will be reset to the read mode " t_{READY} " after the \overline{RESET} pin is driven low. Furthermore, once the \overline{RESET} pin goes high, the devices require an additional " t_{RH} " before it will allow read access. When the \overline{RESET} pin is low, the devices will be in the standby mode for the duration of the pulse and all the data output pins will be tri-stated. If a hardware reset occurs during a program or erase operation, the data at that particular location will be corrupted. Please note that the \overline{RESET} output signal should be ignored during the \overline{RESET} pulse. See Figure 14 for the timing diagram. Refer to Temporary Sector Group Unprotection for additional functionality.

Boot Block Sector Protection

The Write Protection function provides a hardware method of protecting certain boot sectors without using V_{ID} . This function is one of two provided by the \overline{WP}/ACC pin.

If the system asserts V_{IL} on the \overline{WP}/ACC pin, the device disables program and erase functions in the two "outermost" 8K byte boot sectors independently of whether those sectors were protected or unprotected using the method described in "Sector Protection/Unprotection". The two outermost 8K byte boot sectors are the two sectors containing the lowest addresses in a bottom-boot-configured device, or the two sectors containing the highest addresses in a top-boot-congfigured device.

(MBM29DL32XTD: SA69 and SA70, MBM29DL32XBD: SA0 and SA1)

If the system asserts $V_{\mathbb{H}}$ on the \overline{WP}/ACC pin, the device reverts to whether the two outermost 8K byte boot sectors were last set to be protected or unprotected. That is, sector protection or unprotection for these two sectors depends on whether they were last protected or unprotected using the method described in "Sector protection/unprotection".

Accelerated Program Operation

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MBM29DL32XTD/BD offers accelerated program operation which enables the programming in high speed. If the system asserts Vacc to the WP/ACC pin, the device automatically enters the acceleration mode and the time required for program operation will reduce to about 60%. This function is primarily intended to allow high speed program, so caution is needed as the sector group will temporarily be unprotected.

The system would use a fact program command sequence when programming during acceleration mode. Set command to fast mode and reset command from fast mode are not necessary. When the device enters the acceleration mode, the device automatically set to fast mode. Therefore, the pressent sequence could be used for programming and detection of completion during acceleration mode.

Removing Vacc from the \overline{WP}/ACC pin returns the device to normal operation. Do not remove Vacc from \overline{WP}/ACC pin while programming. See Figure 21.

Table 12 MBM29DL32XTD/BD Command Definitions

Comma sequen		Bus write cycles	First write		Second write of		Third write		Fourth read/v	write	Fifth write		Sixth write o	
ooquon		req'd	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data
Read/Reset	Word Byte	1	XXXH	F0H	_	_	_	_		_		_		
Read/Reset	Word Byte	3	555H AAAH	AAH	2AAH 555H	55H	555H AAAH	F0H	RA	RD	_	_	_	_
Autoselect	Word	3	555H	AAH	2AAH	55H	(BA) 555H	90H						
Autoscicut	Byte	3	AAAH	7001	555H	3311	(BA) AAAH	3011						
Program	Word Byte	4	555H AAAH	AAH	2AAH 555H	55H	555H AAAH	A0H	PA	PD	_	_	_	_
Program Suspe	end	1	BA	ВОН	_	_	_			_	_		_	
Program Resu	me	1	BA	30H	_					_				
Chip Erase	Word Byte	6	555H AAAH	ААН	2AAH 555H	55H	555H AAAH	80H	555H AAAH	ААН	2AAH 555H	55H	555H AAAH	10H
Sector Erase	Word Byte	6	555H AAAH	ААН	2AAH 555H	55H	555H AAAH	80H	555H AAAH	ААН	2AAH 555H	55H	SA	30H
Erase Susp	end	1	BA	ВОН		_	_	_	_	_	_	_	_	_
Erase Resu		1	BA	30H		_	_	_	_	_	_	_	_	_
Set to Fast Mode	Word Byte	3	555H AAAH	ААН	2AAH 555H	55H	555H AAAH	20H	_	_	_	_	_	_
Fast Program *1	Word Byte	2	XXXH	A0H	PA	PD	_	_		_	_	_	_	_
Reset from Fast Mode *1	Word Byte	2	BA BA	90H	XXXH XXXH	F0H	_		_		_		_	
Extended Sector Group Protection *2	Word Byte	4	XXXH	60H	SPA	60H	SPA	40H	SPA	SD	_		_	_
Query *3	Word Byte	1	55H AAH	98H	-	_	_	_	_	_	_	_	_	_
Hi-ROM Entry	Word Byte	3	555H AAAH	AAH	2AAH 555H	55H	555H AAAH	88H	_	_	_	_	_	_
Hi-ROM Program *4	Word Byte	4	555H AAAH	AAH	2AAH 555H	55H	555H AAAH	A0H	PA	PD	_	_	_	_
Hi-ROM Erase *4	Word Byte	6	555H AAAH	AAH	2AAH 555H	55H	555H AAAH	80H	555H AAAH	AAH	2AAH 555H	55H	HRA	30H
Hi-ROM	Word	4	555H	AAH	2AAH	55H	(HRBA) 555H	90H	XXXH	00H				
Exit *4	Byte	4	AAAH	ААП	555H	ออก	(HRBA) AAAH	900	^^^П	UUI	_	_	_	_

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- Notes: 1. Address bits A_{11} to $A_{20} = X =$ "H" or "L" for all address commands except or Program Address (PA), Sector Address (SA), and Bank Address (BA).
 - 2. Bus operations are defined in Tables 3 and 4.
 - 3. RA = Address of the memory location to be read
 - PA = Address of the memory location to be programmed
 Addresses are latched on the falling edge of the write pulse.
 - SA = Address of the sector to be erased. The combination of A₂₀, A₁₉, A₁₈, A₁₇, A₁₆, A₁₅, A₁₄, A₁₃, and A₁₂ will uniquely select any sector.
 - BA = Bank Address (A₁₅ to A₂₀)
 - 4. RD = Data read from location RA during read operation.
 - PD = Data to be programmed at location PA. Data is latched on the falling edge of write pulse.
 - 5. SPA = Sector group address to be protected. Set sector group address (SGA) and $(A_6, A_1, A_0) = (0, 1, 0)$.
 - SD = Sector group protection verify data. Output 01H at protected sector group addresses and output 00H at unprotected sector group addresses.
 - 6. HRA = Address of the Hi-ROM area

29DL32XTD (Top Boot Type) Word Mode: 1F8000H to 1FFFFFH

Byte Mode: 3F0000H to 3FFFFFH

29DL32XBD (Bottom Boot Type) Word Mode: 000000H to 007FFFH

Byte Mode: 000000H to 00FFFFH

7. HRBA =Bank Address of the Hi-ROM area

29DL32XTD (Top Boot Type) $:A_{15} = A_{16} = A_{17} = A_{18} = A_{19} = A_{20} = 1$

29DL32XBD (Bottom Boot Type) : $A_{15} = A_{16} = A_{17} = A_{18} = A_{19} = A_{20} = 0$

8. The system should generate the following address patterns:

Word Mode: 555H or 2AAH to addresses A₀ to A₁₀

Byte Mode: AAAH or 555H to addresses A-1 and A₀ to A₁₀

- 9. Both Read/Reset commands are functionally equivalent, resetting the device to the read mode.
- *1:This command is valid while Fast Mode.
- *2:This command is valid while $\overline{RESET} = V_{ID}$.
- www.Dat3.The valid addresses are A6 to A0.
 - *4:This command is valid while Hi-ROM mode.

■ COMMAND DEFINITIONS

Device operations are selected by writing specific address and data sequences into the command register. Writing incorrect address and data values or writing them in the improper sequence will reset the devices to the read mode. Some commands are required Bank Address (BA) input. When command sequences are inputed to bank being read, the commands have priority than reading. Table 12 defines the valid register command sequences. Note that the Erase Suspend (B0H) and Erase Resume (30H) commands are valid only while the Sector Erase operation is in progress. Also the Program Suspend (B0H) and Program Resume (30H) commands are valid only while the Program operation is in progress. Moreover both Read/Reset commands are functionally equivalent, resetting the device to the read mode. Please note that commands are always written at DQ $_0$ to DQ $_7$ and DQ $_8$ to DQ $_{15}$ bits are ignored.

Read/Reset Command

In order to return from Autoselect mode or Exceeded Timing Limits ($DQ_5 = 1$) to Read/Reset mode, the Read/Reset operation is initiated by writing the Read/Reset command sequence into the command register. Microprocessor read cycles retrieve array data from the memory. The devices remain enabled for reads until the command register contents are altered.

The devices will automatically power-up in the Read/Reset state. In this case, a command sequence is not required to read data. Standard microprocessor read cycles will retrieve array data. This default value ensures that no spurious alteration of the memory content occurs during the power transition. Refer to the AC Read Characteristics and Waveforms for the specific timing parameters.

Autoselect Command

Flash memories are intended for use in applications where the local CPU alters memory contents. As such, manufacture and device codes must be accessible while the devices reside in the target system. PROM programmers typically access the signature codes by raising A₉ to a high voltage. However, multiplexing high voltage onto the address lines is not generally desired system design practice.

The device contains an Autoselect command operation to supplement traditional PROM programming www.DataSmethodology. The operation is initiated by writing the Autoselect command sequence into the command register.

The Autoselect command sequence is initiated by first writing two unlock cycles. This is followed by a third write cycle that contains the bank address (BA) and the Autoselect command. Then the manufacture and device codes can be read from the bank, and an actual data of memory cell can be read from the another bank.

Following the command write, a read cycle from address (BA)00H retrieves the manufacture code of 04H. A read cycle from address (BA)01H for \times 16((BA)02H for \times 8) returns the device code (MBM29DL321TD = 59H and MBM29DL321BD = 5AH for \times 8 mode; MBM29DL321TD = 2259H and MBM29DL322TD = 225AH for \times 16 mode). (MBM29DL322TD = 55H and MBM29DL322BD = 56H for \times 8 mode; MBM29DL322TD = 2255H and MBM29DL322BD = 2256H for \times 16 mode). (MBM29DL323TD = 50H and MBM29DL323BD = 53H for \times 8 mode; MBM29DL323TD = 2250H and MBM29DL323BD = 2253H for \times 16 mode). (MBM29DL324TD = 5CH and MBM29DL324BD = 5FH for \times 8 mode; MBM29DL324TD = 225CH and MBM29DL324BD = 225FH for \times 16 mode). (See Tables 11.1 to 11.8.)

All manufacturer and device codes will exhibit odd parity with DQ $_7$ defined as the parity bit. Sector state (protection or unprotection) will be informed by address (BA)02H for ×16 ((BA)04H for ×8). Scanning the sector group addresses (A $_{20}$, A $_{19}$, A $_{18}$, A $_{17}$, A $_{16}$, A $_{15}$, A $_{14}$, A $_{13}$, and A $_{12}$) while (A $_{6}$, A $_{1}$, A $_{0}$) = (0, 1, 0) will produce a logical "1" at device output DQ $_{0}$ for a protected sector group. The programming verification should be performed by verify sector group protection on the protected sector. (See Tables 8 and 9.)

The manufacture and device codes can be allowed reading from selected bank. To read the manufacture and device codes and sector protection status from non-selected bank, it is necessary to write Read/Reset command sequence into the register and then Autoselect command should be written into the bank to be read.

If the software (program code) for Autoselect command is stored into the Flash memory, the device and manufacture codes should be read from the other bank where is not contain the software.

To terminate the operation, it is necessary to write the Read/Reset command sequence into the register, and also to write the Autoselect command during the operation, execute it after writing Read/Reset command sequence.

Byte/Word Programming

The devices are programmed on a byte-by-byte (or word-by-word) basis. Programming is a four bus cycle operation. There are two "unlock" write cycles. These are followed by the program set-up command and data write cycles. Addresses are latched on the falling edge of \overline{CE} or \overline{WE} , whichever happens later and the data is latched on the rising edge of \overline{CE} or \overline{WE} , whichever happens first. The rising edge of \overline{CE} or \overline{WE} (whichever happens first) begins programming. Upon executing the Embedded Program Algorithm command sequence, the system is not required to provide further controls or timings. The device will automatically provide adequate internally generated program pulses and verify the programmed cell margin.

The system can determine the status of the program operation by using DQ₇ (Data Polling), DQ₆ (Toggle Bit), or RY/BY. The Data Polling and Toggle Bit must be performed at the memory location which is being programmed.

The automatic programming operation is completed when the data on DQ_7 is equivalent to data written to this bit at which time the devices return to the read mode and addresses are no longer latched. (See Table 13, Hardware Sequence Flags.) Therefore, the devices require that a valid address to the devices be supplied by the system at this particular instance of time. Hence, \overline{Data} Polling must be performed at the memory location which is being programmed.

Any commands written to the chip during this period will be ignored. If hardware reset occurs during the programming operation, it is impossible to guarantee the data are being written.

Programming is allowed in any sequence and across sector boundaries. Beware that a data "0" cannot be programmed back to a "1". Attempting to do so may either hang up the device or result in an apparent success according to the data polling algorithm but a read from Read/Reset mode will show that the data is still "0". Only erase operations can convert "0"s to "1"s.

Figure 22 illustrates the Embedded Program™ Algorithm using typical command strings and bus operations.

Chip Erase

Chip erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the chip erase command.

Chip erase does not require the user to program the device prior to erase. Upon executing the Embedded Erase Algorithm command sequence the devices will automatically program and verify the entire memory for an all zero data pattern prior to electrical erase (Preprogram function). The system is not required to provide any controls or timings during these operations.

The system can determine the status of the erase operation by using DQ_7 (\overline{Data} Polling), DQ_6 (Toggle Bit), or RY/ \overline{BY} . The chip erase begins on the rising edge of the last \overline{CE} or \overline{WE} , whichever happens first in the command sequence and terminates when the data on DQ_7 is "1" (See Write Operation Status section.) at which time the device returns to read the mode.

Chip Erase Time; Sector Erase Time × All sectors + Chip Program Time (Preprogramming)

Figure 23 illustrates the Embedded Erase™ Algorithm using typical command strings and bus operations.

Sector Erase

Sector erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the Sector Erase command. The sector address (any address location within the desired sector) is latched on the falling edge of $\overline{\text{CE}}$ or $\overline{\text{WE}}$ whichever happens later, while the command (Data = 30H) is latched on the rising edge of $\overline{\text{CE}}$ or $\overline{\text{WE}}$ which happens first. After time-out of "t_{TOW}" from the rising edge of the last sector erase command, the sector erase operation will begin.

Multiple sectors may be erased concurrently by writing the six bus cycle operations on Table 12. This sequence is followed with writes of the Sector Erase command to addresses in other sectors desired to be concurrently erased. The time between writes must be less than " t_{TOW} " otherwise that command will not be accepted and erasure will start. It is recommended that processor interrupts be disabled during this time to guarantee this condition. The interrupts can be re-enabled after the last Sector Erase command is written. A time-out of " t_{TOW} " from the rising edge of last \overline{CE} or \overline{WE} whichever happens first will initiate the execution of the Sector Erase command(s). If another falling edge of \overline{CE} or \overline{WE} , whichever happens first occurs within the " t_{TOW} " time-out window the timer is reset. (Monitor DQ_3 to determine if the sector erase timer window is still open, see section DQ_3 , Sector Erase Timer.) Any command other than Sector Erase or Erase Suspend during this time-out period will reset the devices to the read mode, ignoring the previous command string. Resetting the devices once execution has begun will corrupt the data in the sector. In that case, restart the erase on those sectors and allow them to complete. (Refer to the Write Operation Status section for Sector Erase Timer operation.) Loading the sector erase buffer may be done in any sequence and with any number of sectors (0 to 38).

Sector erase does not require the user to program the devices prior to erase. The devices automatically program all memory locations in the sector(s) to be erased prior to electrical erase (Preprogram function). When erasing a sector or sectors the remaining unselected sectors are not affected. The system is not required to provide any controls or timings during these operations.

The system can determine the status of the erase operation by using DQ_7 (\overline{Data} Polling), DQ_6 (Toggle Bit), or RY/ \overline{BY} .

The sector erase begins after the "trow" time out from the rising edge of \overline{CE} or \overline{WE} whichever happens first for the last sector erase command pulse and terminates when the data on DQ₇ is "1" (See Write Operation Status www.DataSsection:) at which time the devices return to the read mode. Data polling and Toggle Bit must be performed at an address within any of the sectors being erased.

Multiple Sector Erase Time; [Sector Erase Time + Sector Program Time (Preprogramming)] × Number of Sector Erase

In case of multiple sector erase across bank boundaries, a read from bank (read-while-erase) can not performe.

Figure 23 illustrates the Embedded Erase™ Algorithm using typical command strings and bus operations.

Erase Suspend/Resume

The Erase Suspend command allows the user to interrupt a Sector Erase operation and then perform data reads from or programs to a sector not being erased. This command is applicable ONLY during the Sector Erase operation which includes the time-out period for sector erase. The Erase Suspend command will be ignored if written during the Chip Erase operation or Embedded Program Algorithm. Writting the Erase Suspend command (B0H) during the Sector Erase time-out results in immediate termination of the time-out period and suspension of the erase operation.

Writing the Erase Resume command (30H) resumes the erase operation. The bank addresses of sector being erasing or suspending should be set when writting the Erase Suspend or Erase Resume command.

When the Erase Suspend command is written during the Sector Erase operation, the device will take a maximum of "tspp" to suspend the erase operation. When the devices have entered the erase-suspended mode, the

RY/ \overline{BY} output pin will be at Hi-Z and the DQ₇ bit will be at logic "1", and DQ₆ will stop toggling. The user must use the address of the erasing sector for reading DQ₆ and DQ₇ to determine if the erase operation has been suspended. Further writes of the Erase Suspend command are ignored.

When the erase operation has been suspended, the devices default to the erase-suspend-read mode. Reading data in this mode is the same as reading from the standard read mode except that the data must be read from sectors that have not been erase-suspended. Successively reading from the erase-suspended sector while the device is in the erase-suspend-read mode will cause DQ₂ to toggle. (See the section on DQ₂.)

After entering the erase-suspend-read mode, the user can program the device by writing the appropriate command sequence for Program. This program mode is known as the erase-suspend-program mode. Again, programming in this mode is the same as programming in the regular Program mode except that the data must be programmed to sectors that are not erase-suspended. Successively reading from the erase-suspended sector while the devices are in the erase-suspend-program mode will cause DQ_2 to toggle. The end of the erase-suspended Program operation is detected by the RY/ \overline{BY} output pin, \overline{Data} polling of DQ_7 or by the Toggle Bit I (DQ_6) which is the same as the regular Program operation. Note that DQ_7 must be read from the Program address while DQ_6 can be read from any address within bank being erase-suspended.

To resume the operation of Sector Erase, the Resume command (30H) should be written to the bank being erase suspended. Any further writes of the Resume command at this point will be ignored. Another Erase Suspend command can be written after the chip has resumed erasing.

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Extended Command

(1) Fast Mode

MBM29DL32XTD/BD has Fast Mode function. This mode dispenses with the initial two unclock cycles required in the standard program command sequence by writing Fast Mode command into the command register. In this mode, the required bus cycle for programming is two cycles instead of four bus cycles in standard program command. (Do not write erase command in this mode.) The read operation is also executed after exiting this mode. To exit this mode, it is necessary to write Fast Mode Reset command into the command register. The first cycle must contain the bank address. (Refer to the Figure 28.) The V_{CC} active current is required even $\overline{CE} = V_{IH}$ during Fast Mode.

(2) Fast Programming

During Fast Mode, the programming can be executed with two bus cycles operation. The Embedded Program Algorithm is executed by writing program set-up command (A0H) and data write cycles (PA/PD). (Refer to the Figure 28.)

(3) Extended Sector Group Protection

In addition to normal sector group protection, the MBM29DL32XTD/BD has Extended Sector Group Protection as extended function. This function enable to protect sector group by forcing $V_{\rm ID}$ on RESET pin and write a command sequence. Unlike conventional procedure, it is not necessary to force $V_{\rm ID}$ and control timing for control pins. The only RESET pin requires $V_{\rm ID}$ for sector group protection in this mode. The extended sector group protection requires $V_{\rm ID}$ on RESET pin. With this condition, the operation is initiated by writing the set-up command (60H) into the command register. Then, the sector group addresses pins (A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{15} , A_{14} , A_{13} and A_{12}) and (A_{6} , A_{1} , A_{0}) = (0, 1, 0) should be set to the sector group to be protected (recommend to set $V_{\rm IL}$ for the other addresses pins), and write extended sector group protection command (60H). A sector group is typically protected in 250 μ s. To verify programming of the protection circuitry, the sector group addresses pins (A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{15} , A_{14} , A_{13} and A_{12}) and (A_{6} , A_{1} , A_{0}) = (0, 1, 0) should be set and write a command (40H). Following the command write, a logical "1" at device output DQ0 will produce for protected sector in the read operation. If the output data is logical "0", please repeat to write extended sector group protection command (60H) again. To terminate the operation, it is necessary to set RESET pin to $V_{\rm IH}$. (Refer to the Figures 20 and 29.)

www.DataS(4):t-CFdo(Common Flash Memory Interface)

The CFI (Common Flash Memory Interface) specification outlines device and host system software interrogation handshake which allows specific vendor-specified software algorithms to be used for entire families of devices. This allows device-independent, JEDEC ID-independent, and forward-and backward-compatible software support for the specified flash device families. Refer to CFI specification in detail.

The operation is initiated by writing the query command (98H) into the command register. The bank address should be set when writing this command. Then the device information can be read from the bank, and an actual data of memory cell be read from the another bank. Following the command write, a read cycle from specific address retrives device information. Please note that output data of upper byte (DQ₈ to DQ₁₅) is "0" in word mode (16 bit) read. Refer to the CFI code table. To terminate operation, it is necessary to write the read/reset command sequence into the register. (See Table 15.)

• Hidden ROM (Hi-ROM) Region

The Hi-ROM feature provides a Flash memory region that the system may access through a new command sequence. This is primarily intended for customers who wish to use an Electronic Serial Number (ESN) in the device with the ESN protected against modification. Once the Hi-ROM region is protected, any further modification of that region is impossible. This ensures the security of the ESN once the product is shipped to the field.

The Hi-ROM region is 64K bytes in length and is stored at the same address of the 8KB ×8 sectors. The MBM29DL32XTD occupies the address of the byte mode 3F0000H to 3FFFFH (word mode 1F8000H to 1FFFFH) and the MBM29DL32XBD type occupies the address of the byte mode 000000H to 00FFFFH (word mode 000000H to 007FFFH). After the system has written the Enter Hi-ROM command sequence, the system may read the Hi-ROM region by using the addresses normally occupied by the boot sectors. That is, the device sends all commands that would normally be sent to the boot sectors to the Hi-ROM region. This mode of operation continues until the system issues the Exit Hi-ROM command sequence, or until power is removed from the device. On power-up, or following a hardware reset, the device reverts to sending commands to the boot sectors.

Hidden ROM (Hi-ROM) Entry Command

MBM29DL32XTD/BD has a Hidden ROM area with One Time Protect function. This area is to enter the security code and to unable the change of the code once set. Program/erase is possible in this area until it is protected. However, once it is protected, it is impossible to unprotect, so please use this with caution.

Hidden ROM area is 64K Byte and in the same address area of 8KB sector. The address of top boot is 3F0000H to 3FFFFFH at byte mode (1F8000H to 1FFFFFH at word mode) and the bottom boot is 000000H to 00FFFFH at byte mode (000000H to 007FFFH at word mode). These areas are normally the boot block area (8KB \times 8 sector). Therefore, write the Hidden ROM entry command sequence to enter the Hidden ROM area. It is called as Hidden ROM mode when the Hidden ROM area appears.

Sector other than the boot block area could be read during Hidden ROM mode. Read/program/earse of the Hidden ROM area is possible during Hidden ROM mode. Write the Hidden ROM reset command sequence to exit the Hidden ROM mode. The bank address of the Hidden ROM should be set on the third cycle of this reset www.DataScommand sequence.

In case of MBM29DL321TD/BD, whose Bank 1 size is 0.5 Mbit, the simultaneous operation cannot execute multi-function mode between the Hidden ROM area and Bank 2 Region.

• Hidden ROM (Hi-ROM) Program Command

To program the data to the Hidden ROM area, write the Hidden ROM program command sequence during Hidden ROM mode. This command is same as the program command in the past except to write the command during Hidden ROM mode. Therefore the detection of completion method is the same as in the past, using the DQ_7 data poling, DQ_6 toggle bit and RY/\overline{BY} pin. Need to pay attention to the address to be programmed. If the address other than the Hidden ROM area is selected to program, the data of the address will be changed.

Hidden ROM (Hi-ROM) Erase Command

To erase the Hidden ROM area, write the Hidden ROM erase command sequence during Hidden ROM mode. This command is same as the sector erase command in the past except to write the command during Hidden ROM mode. Therefore the detection of completion method is the same as in the past, using the DQ_7 data poling, DQ_6 toggle bit and RY/\overline{BY} pin. Need to pay attention to the sector address to be erased. If the sector address other than the Hidden ROM area is selected, the data of the sector will be changed.

Hidden ROM (Hi-ROM) Protect Command

There are two methods to protect the Hidden ROM area. One is to write the sector group protect setup command(60H), set the sector address in the Hidden ROM area and $(A_6, A_1, A_0) = (0,1,0)$, and write the sector group protect command(60H) during the Hidden ROM mode. The same command sequence could be used because except that it is in the Hidden ROM mode and that it does not apply high voltage to \overline{RESET} pin, it is the same as the extension sector group protect in the past. Please refer to "Function Explanation **Extended Command** (3) Extentended Sector Group Protection" for details of extention sector group protect setting.

The other is to apply high voltage (V_{ID}) to A_{9} and \overline{OE} , set the sector address in the Hidden ROM area and (A_{6} , A_{1} , A_{0}) = (0,1,0), and apply the write pulse during the Hidden ROM mode. To verify the protect circuit, apply high voltage (V_{ID}) to A_{9} , specify (A_{6} , A_{1} , A_{0}) = (0,1,0) and the sector address in the Hidden ROM area, and read. When "1" appears to DQ_{0} , the protect setting is completed. "0" will appear to DQ_{0} if it is not protected. Please apply write pulse agian. The same command sequence could be used for the above method because other than the Hidden ROM mode, it is the same as the sector group protect in the past. Please refer to "Function Explanation **Secor Group Protection**" for details of sector group protect setting

Other sector group will be effected if the address other than the Hidden ROM area is selected for the sectoer group address, so please be carefull. Once it is protected, protection can not be cancelled, so please pay closest attention.

Write Operation Status

Detailed in Table 13 are all the status flags that can determine the status of the bank for the current mode operation. The read operation from the bank where is not operate Embedded Algorithm returns a data of memory cell. These bits offer a method for determining whether a Embedded Algorithm is completed properly. The information on DQ₂ is address sensitive. This means that if an address from an erasing sector is consectively read, then the DQ₂ bit will toggle. However, DQ₂ will not toggle if an address from a non-erasing sector is consectively read. This allows the user to determine which sectors are erasing and which are not.

The status flag is not output from bank (non-busy bank) not executing Embedded Algorithm. For example, there is bank (busy bank) which is now executing Embedded Algorithm. When the read sequence is [1] <busy bank>, www.DataS[2]***Hon-busy bank>, [3] <busy bank>, the DQ6 is toggling in the case of [1] and [3]. In case of [2], the data of memory cell is outputted. In the erase-suspend read mode with the same read sequence, DQ6 will not be toggled in the [1] and [3].

In the erase suspend read mode, DQ₂ is toggled in the [1] and [3]. In case of [2], the data of memory cell is outputted.

Table 13 Hardware Sequence Flags

		Status	DQ ₇	DQ ₆	DQ ₅	DQ ₃	DQ ₂
	Embedded F	Program Algorithm	DQ ₇	Toggle	0	0	1
	Embedded E	rase Algorithm	0	Toggle	0	1	Toggle*
	Program	Program Suspend Read (Program Suspended Sector)	Data	Data	Data	Data	Data
In Progress	Suspended Mode	Program Suspend Read (Non-Program Suspended Sector)	Data	Data	Data	Data	Data
		Erase Suspend Read (Erase Suspended Sector)	1	1	0	0 1 a Data a Data 0	Toggle
	Erase Suspended Mode	Erase Suspend Read (Non-Erase Suspended Sector)	Data	Data	Data	Data	Data
		Erase Suspend Program (Non-Erase Suspended Sector)	DQ ₇	Toggle	0	0	1*
	Embedded F	Program Algorithm	DQ 7	Toggle	1	0	1
Exceeded	Embedded E	rase Algorithm	0	Toggle	1	1	N/A
Time Limits	Erase Suspended Mode	Erase Suspend Program (Non-Erase Suspended Sector)	DQ ₇	Toggle	1	0	N/A

^{*:} Successive reads from the erasing or erase-suspend sector will cause DQ2 to toggle. Reading from non-erase suspend sector address will indicate logic "1" at the DQ2 bit.

Note: 1.DQo and DQ1 are reserve pins for future use.

2.DQ4 is Fujitsu internal use only.

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• DQ7

Data Polling

The MBM29DL32XTD/BD devices feature \overline{Data} Polling as a method to indicate to the host that the Embedded Algorithms are in progress or completed. During the Embedded Program Algorithm an attempt to read the devices will produce the complement of the data last written to DQ_7 . Upon completion of the Embedded Program Algorithm, an attempt to read the device will produce the true data last written to DQ_7 . During the Embedded Erase Algorithm, an attempt to read the device will produce a "0" at the DQ_7 output. Upon completion of the Embedded Erase Algorithm an attempt to read the device will produce a "1" at the DQ_7 output. The flowchart for \overline{Data} Polling (DQ_7) is shown in Figure 24.

For programming, the Data Polling is valid after the rising edge of fourth write pulse in the four write pulse sequence.

For chip erase and sector erase, the Data Polling is valid after the rising edge of the sixth write pulse in the six write pulse sequence. Data Polling must be performed at sector address within any of the sectors being erased and not a protected sector. Otherwise, the status may not be valid.

If a program address falls within a protected sector, \overline{Data} Polling on DQ₇ is active for approximately 1 μ s, then that bank returns to the read mode. After an erase command sequence is written, if all sectors selected for erasing are protected, \overline{Data} Polling on DQ₇ is active for approximately 400 μ s, then the bank returns to read mode.

Once the Embedded Algorithm operation is close to being completed, the MBM29DL32XTD/BD data pins (DQ $_7$) may change asynchronously while the output enable (\overline{OE}) is asserted low. This means that the devices are driving status information on DQ $_7$ at one instant of time and then that byte's valid data at the next instant of time. Depending on when the system samples the DQ $_7$ output, it may read the status or valid data. Even if the device has completed the Embedded Algorithm operation and DQ $_7$ has a valid data, the data outputs on DQ $_0$ to DQ $_6$ may be still invalid. The valid data on DQ $_0$ to DQ $_7$ will be read on the successive read attempts.

The Data Polling feature is only active during the Embedded Programming Algorithm, Embedded Erase Algorithm or sector erase time-out. (See Table 13.)

See Figure 9 for the Data Polling timing specifications and diagrams.

• DQ₆

Toggle Bit I

The MBM29DL32XTD/BD also feature the "Toggle Bit I" as a method to indicate to the host system that the Embedded Algorithms are in progress or completed.

During an Embedded Program or Erase Algorithm cycle, successive attempts to read (\overline{OE} toggling) data from the devices will result in DQ6 toggling between one and zero. Once the Embedded Program or Erase Algorithm cycle is completed, DQ6 will stop toggling and valid data will be read on the next successive attempts. During programming, the Toggle Bit I is valid after the rising edge of the fourth write pulse in the four write pulse sequence. For chip erase and sector erase, the Toggle Bit I is valid after the rising edge of the sixth write pulse in the six write pulse sequence. The Toggle Bit I is active during the sector time out.

In programming, if the sector being written to is protected, the toggle bit will toggle for about 1 μ s and then stop toggling without the data having changed. In erase, the devices will erase all the selected sectors except for the ones that are protected. If all selected sectors are protected, the chip will toggle the toggle bit for about 400 μ s and then drop back into read mode, having changed none of the data.

Either \overline{CE} or \overline{OE} toggling will cause the DQ6 to toggle. In addition, an Erase Suspend/Resume command will cause the DQ6 to toggle.

The system can use DQ_6 to determine whether a sector is actively erasing or is erase-suspended. When a bank is actively erasing (that is, the Embedded Erase Algorithm is in progress), DQ_6 toggles. When a bank enters the Erase Suspend mode, DQ_6 stops toggling. Successive read cycles during the erase-suspend-program cause DQ_6 to toggle.

To operate toggle bit function properly, $\overline{\text{CE}}$ or $\overline{\text{OE}}$ must be high when bank address is changed.

See Figure 10 for the Toggle Bit I timing specifications and diagrams.

• DQ5

Exceeded Timing Limits

 DQ_5 will indicate if the program or erase time has exceeded the specified limits (internal pulse count). Under these conditions DQ_5 will produce a "1". This is a failure condition which indicates that the program or erase cycle was not successfully completed. \overline{Data} Polling is the only operating function of the devices under this condition. The \overline{CE} circuit will partially power down the device under these conditions (to approximately 2 mA). The \overline{OE} and \overline{WE} pins will control the output disable functions as described in Tables 3 and 4.

The DQ_5 failure condition may also appear if a user tries to program a non blank location without erasing. In this case the devices lock out and never complete the Embedded Algorithm operation. Hence, the system never reads a valid data on DQ_7 bit and DQ_6 never stops toggling. Once the devices have exceeded timing limits, the DQ_5 bit will indicate a "1." Please note that this is not a device failure condition since the devices were incorrectly used. If this occurs, reset the device with command sequence.

• DQ3

Sector Erase Timer

After the completion of the initial sector erase command sequence the sector erase time-out will begin. DQ3 will remain low until the time-out is complete. Data Polling and Toggle Bit are valid after the initial sector erase command sequence.

If Data Polling or the Toggle Bit I indicates the device has been written with a valid erase command, DQ₃ may www.DataSbe_used_to determine if the sector erase timer window is still open. If DQ₃ is high ("1") the internally controlled erase cycle has begun; attempts to write subsequent commands to the device will be ignored until the erase operation is completed as indicated by Data Polling or Toggle Bit I. If DQ₃ is low ("0"), the device will accept additional sector erase commands. To insure the command has been accepted, the system software should check the status of DQ₃ prior to and following each subsequent Sector Erase command. If DQ₃ were high on the second status check, the command may not have been accepted.

See Table 13: Hardware Sequence Flags.

• DQ₂

Toggle Bit II

This toggle bit II, along with DQ₆, can be used to determine whether the devices are in the Embedded Erase Algorithm or in Erase Suspend.

Successive reads from the erasing sector will cause DQ_2 to toggle during the Embedded Erase Algorithm. If the devices are in the erase-suspended-read mode, successive reads from the erase-suspended sector will cause DQ_2 to toggle. When the devices are in the erase-suspended-program mode, successive reads from the byte address of the non-erase suspended sector will indicate a logic "1" at the DQ_2 bit.

 DQ_6 is different from DQ_2 in that DQ_6 toggles only when the standard program or Erase, or Erase Suspend Program operation is in progress. The behavior of these two status bits, along with that of DQ_7 , is summarized as follows:

For example, DQ₂ and DQ₆ can be used together to determine if the erase-suspend-read mode is in progress. (DQ₂ toggles while DQ₆ does not.) See also Table 14 and Figure 12.

Furthermore, DQ₂ can also be used to determine which sector is being erased. When the device is in the erase mode, DQ₂ toggles if this bit is read from an erasing sector.

To operate toggle bit function properly, $\overline{\mathsf{CE}}$ or $\overline{\mathsf{OE}}$ must be high when bank address is changed.

Mode DQ₇ DQ_6 DQ_2 \overline{DQ}_7 Program Toggle Erase 0 Toggle Toggle (Note) **Erase-Suspend Read** 1 1 Toggle (Erase-Suspended Sector) DQ₇ **Erase-Suspend Program** Toggle 1 (Note)

Table 14 Toggle Bit Status

Note: Successive reads from the erasing or erase-suspend sector will cause DQ2 to toggle. Reading from nonerase suspend sector address will indicate logic "1" at the DQ2 bit.

• RY/BY

Ready/Busy

The MBM29DL32XTD/BD provide a RY/BY open-drain output pin as a way to indicate to the host system that the Embedded Algorithms are either in progress or has been completed. If the output is low, the devices are busy with either a program or erase operation. If the output is high, the devices are ready to accept any read/write or erase operation. When the RY/BY pin is low, the devices will not accept any additional program or erase commands. If the MBM29DL32XTD/BD are placed in an Erase Suspend mode, the RY/BY output will be high.

During programming, the RY/BY pin is driven low after the rising edge of the fourth write pulse. During an erase operation, the RY/BY pin is driven low after the rising edge of the sixth write pulse. The RY/BY pin will indicate a busy condition during the RESET pulse. Refer to Figures 13 and 14 for a detailed timing diagram. The RY/BY www.DataSpintis pulled high in standby mode.

Since this is an open-drain output, RY/BY pins can be tied together in parallel with a pull-up resistor to Vcc.

Byte/Word Configuration

The $\overline{\text{BYTE}}$ pin selects the byte (8-bit) mode or word (16-bit) mode for the MBM29DL32XTD/BD devices. When this pin is driven high, the devices operate in the word (16-bit) mode. The data is read and programmed at DQ0 to DQ15. When this pin is driven low, the devices operate in byte (8-bit) mode. Under this mode, the DQ15/A-1 pin becomes the lowest address bit and DQ8 to DQ14 bits are tri-stated. However, the command bus cycle is always an 8-bit operation and hence commands are written at DQ0 to DQ7 and the DQ8 to DQ15 bits are ignored. Refer to Figures 15, 16 and 17 for the timing diagram.

• Data Protection

The MBM29DL32XTD/BD are designed to offer protection against accidental erasure or programming caused by spurious system level signals that may exist during power transitions. During power up the devices automatically reset the internal state machine in the Read mode. Also, with its control register architecture, alteration of the memory contents only occurs after successful completion of specific multi-bus cycle command sequences.

The devices also incorporate several features to prevent inadvertent write cycles resulting form Vcc power-up and power-down transitions or system noise.

• Low Vcc Write Inhibit

To avoid initiation of a write cycle during $V_{\rm CC}$ power-up and power-down, a write cycle is locked out for $V_{\rm CC}$ less than $V_{\rm LKO}$ (min). If $V_{\rm CC} < V_{\rm LKO}$, the command register is disabled and all internal program/erase circuits are disabled. Under this condition the device will reset to the read mode. Subsequent writes will be ignored until the $V_{\rm CC}$ level is greater than $V_{\rm LKO}$. It is the users responsibility to ensure that the control pins are logically correct to prevent unintentional writes when $V_{\rm CC}$ is above $V_{\rm LKO}$ (min).

If Embedded Erase Algorithm is interrupted, there is possibility that the erasing sector(s) cannot be used.

• Write Pulse "Glitch" Protection

Noise pulses of less than 5 ns (typical) on \overline{OE} , \overline{CE} , or \overline{WE} will not initiate a write cycle.

Logical Inhibit

Writing is inhibited by holding any one of $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IH}$, or $\overline{WE} = V_{IH}$. To initiate a write cycle \overline{CE} and \overline{WE} must be a logical zero while \overline{OE} is a logical one.

• Power-Up Write Inhibit

Power-up of the devices with $\overline{WE} = \overline{CE} = V_{IL}$ and $\overline{OE} = V_{IH}$ will not accept commands on the rising edge of \overline{WE} . The internal state machine is automatically reset to the read mode on power-up.

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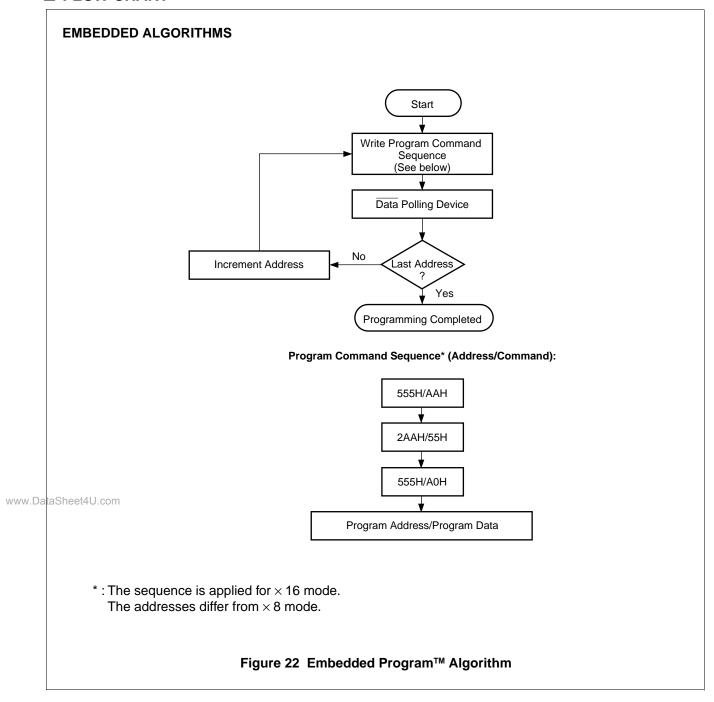
Table 15 Common Flash Memory Interface Code

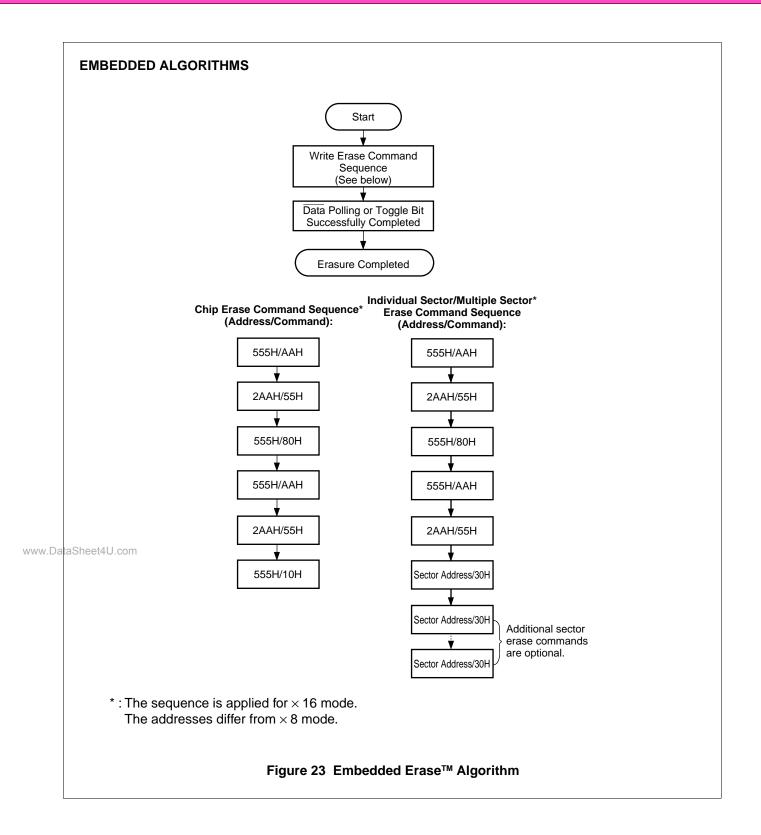
	Description	A ₀ to A ₆	DQ ₀ to DQ ₁₅
	Query-unique ASCII string	10h	0051h
	"QRY"	11h	0052h
		12h	0059h
	Primary OEM Command Set	13h	0002h
	2h: AMD/FJ standard type	14h	0000h
	Address for Primary	15h	0040h
	Extended Table	16h	0000h
	Alternate OEM Command	17h	0000h
	Set (00h = not applicable)	18h	0000h
	Address for Alternate OEM	19h	0000h
	Extended Table	1Ah	0000h
	Vcc Min. (write/erase) D7-4: volt, D3-0: 100 mvolt	1Bh	0027h
	Vcc Max. (write/erase) D7-4: volt, D3-0: 100 mvolt	1Ch	0036h
	V _{PP} Min. voltage	1Dh	0000h
	V _{PP} Max. voltage	1Eh	0000h
www.D	Typical timeout per single byte/word write 2 ^N μs	1Fh	0004h
	Typical timeout for Min. size buffer write 2 ^N μs	20h	0000h
	Typical timeout per individual block erase 2 ^N ms	21h	000Ah
	Typical timeout for full chip erase 2 ^N ms	22h	0000h
	Max. timeout for byte/word write 2 ^N times typical	23h	0005h
	Maxetimeout for buffer write 2 ^N times typical	24h	0000h
	Max. timeout per individual block erase 2 ^N times typical	25h	0004h
	Max. timeout for full chip erase 2 ^N times typical	26h	0000h
	Device Size = 2 ^N byte	27h	0016h
	Flash Device Interface	28h	0002h
	description	29h	0000h
	Max. number of byte in	2Ah	0000h
	multi-byte write = 2 ^N	2Bh	0000h
	Number of Erase Block Regions within device	2Ch	0002h
	Erase Block Region 1	2Dh	0007h
	Information	2Eh	0000h
		2Fh	0020h
		30h	0000h
	Erase Block Region 2	31h	003Eh
	Information	32h	0000h
		33h	0000h
		34h	0001h

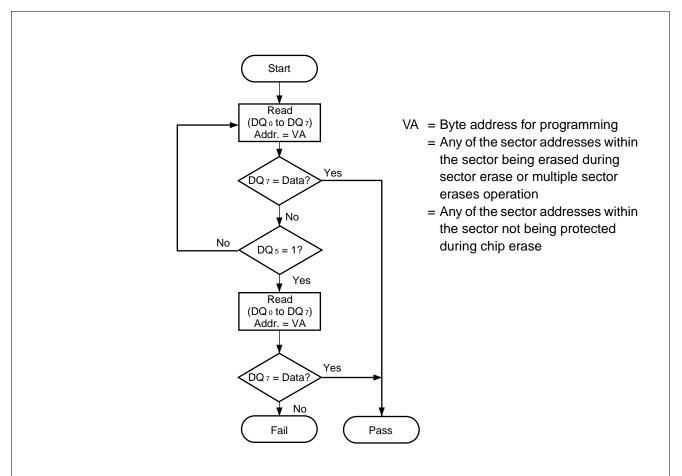
Description	A ₀ to A ₆	DQ ₀ to DQ ₁₅
•		** **
Query-unique ASCII string "PRI"	40h 41h	0050h 0052h
110	4111 42h	003211 0049h
Major version number, ASCII	43h	004311 0031h
Minor version number, ASCII	44h	0031h
Address Sensitive Unlock	45h	0000h
0h = Required 1h = Not Required	4311	000011
Erase Suspend 0h = Not Supported 1h = To Read Only 2h = To Read & Write	46h	0002h
Sector Protection 0h = Not Supported X = Number of sectors in per group	47h	0001h
Sector Temporary Unprotection 00h = Not Supported 01h = Supported	48h	0001h
Sector Protection Algorithm	49h	0004h
Number of Sector for Bank 2 00h = Not Supported 3Fh = MBM29DL321TD 38h = MBM29DL322TD 30h = MBM29DL323TD 20h = MBM29DL324TD 3Fh = MBM29DL321BD 38h = MBM29DL322BD 30h = MBM29DL323BD 20h = MBM29DL324BD	4Ah	00XXh
Burst Mode Type 00h = Not Supported	4Bh	0000h
Page Mode Type 00h = Not Supported	4Ch	0000h
ACC (Acceleration) Supply Minimum 00h = Not Supported, D7-4: volt, D3-0: 100 mvolt	4Dh	0085h
ACC (Acceleration) Supply Maximum 00h = Not Supported, D7-4: volt, D3-0: 100 mvolt	4Eh	0095h
Boot Type 02h = MBM29DL32XBD 03h = MBM29DL32XTD	4Fh	00XXh

72

■ FLOW CHART

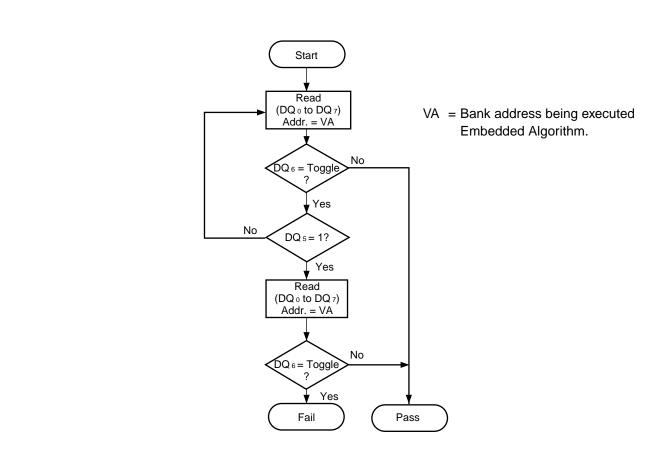






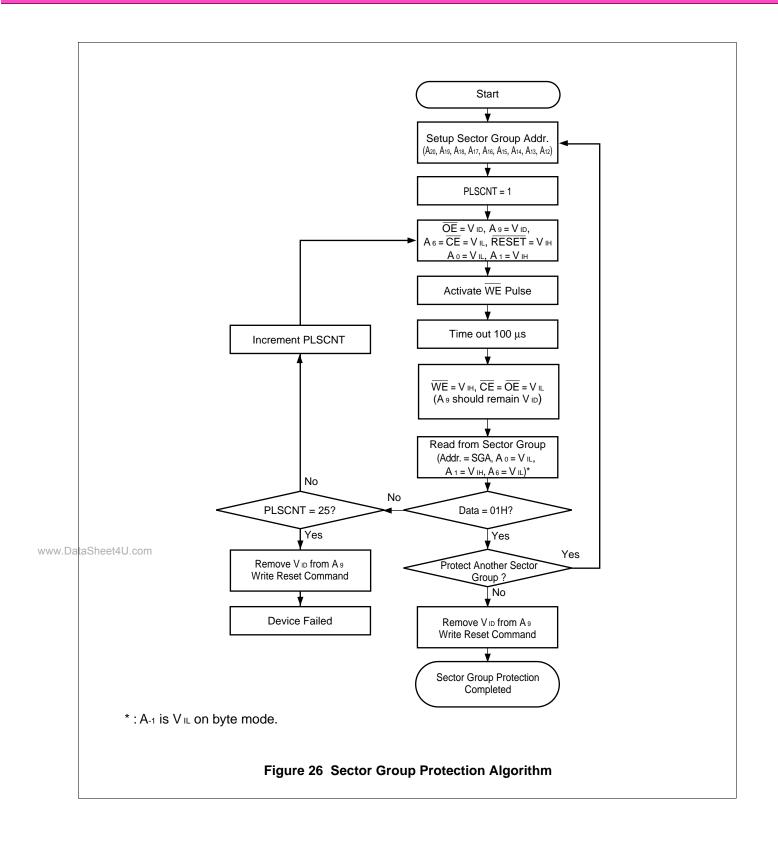
Note: DQ_7 is rechecked even if DQ_5 = "1" because DQ_7 may change simultaneously with DQ_5 .

Figure 24 Data Polling Algorithm



Note: DQ $_6$ is rechecked even if DQ $_5$ = "1" because DQ $_6$ may stop toggling at the same time as DQ $_5$ changing to "1".

Figure 25 Toggle Bit Algorithm



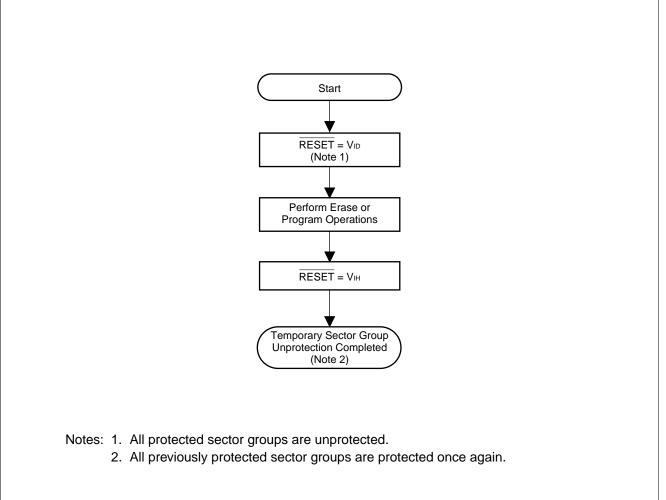
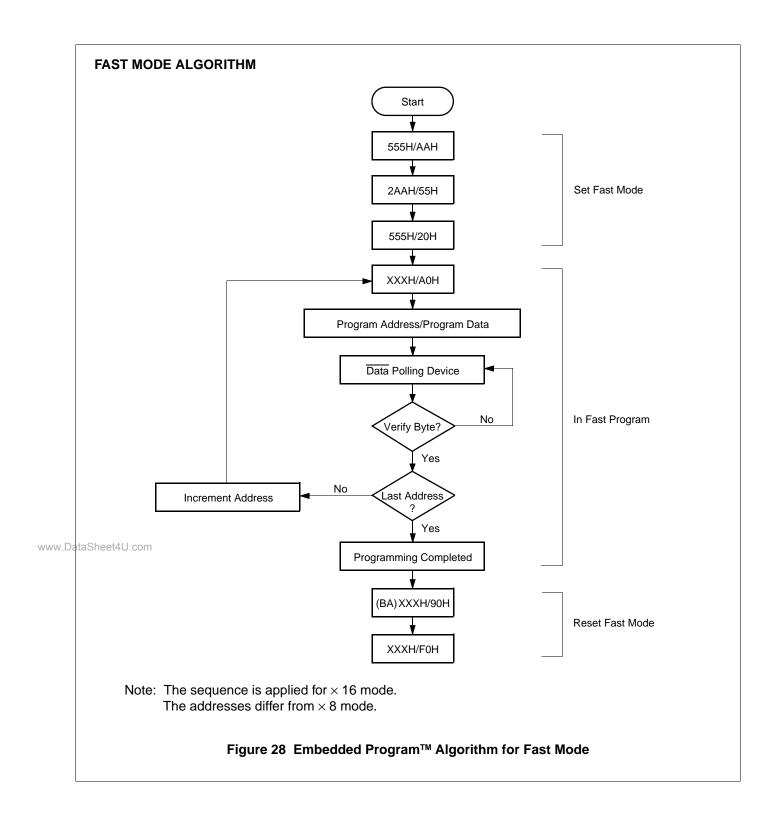
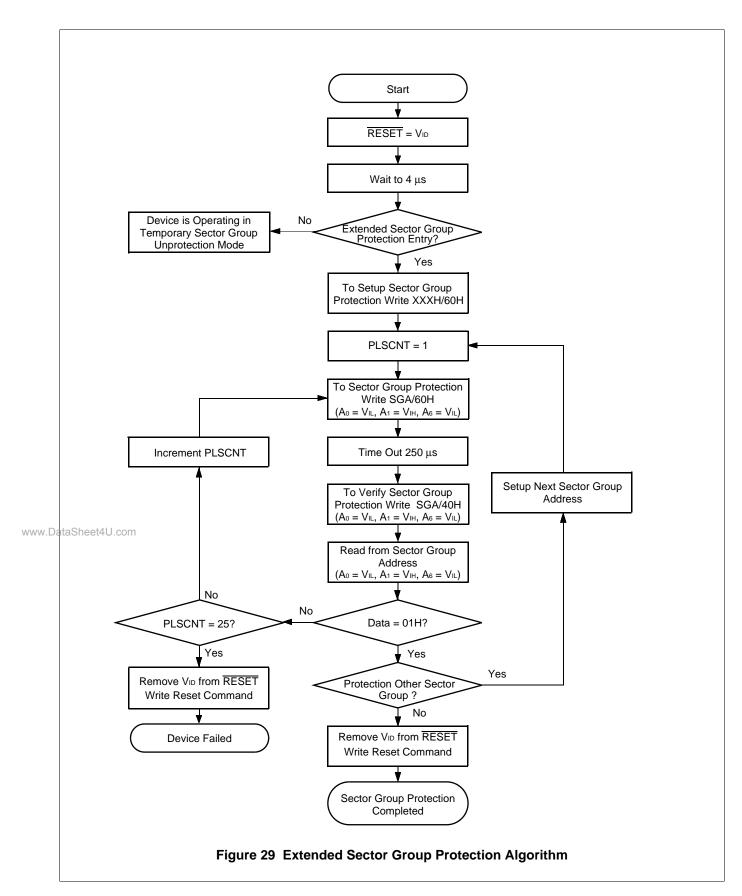


Figure 27 Temporary Sector Group Unprotection Algorithm

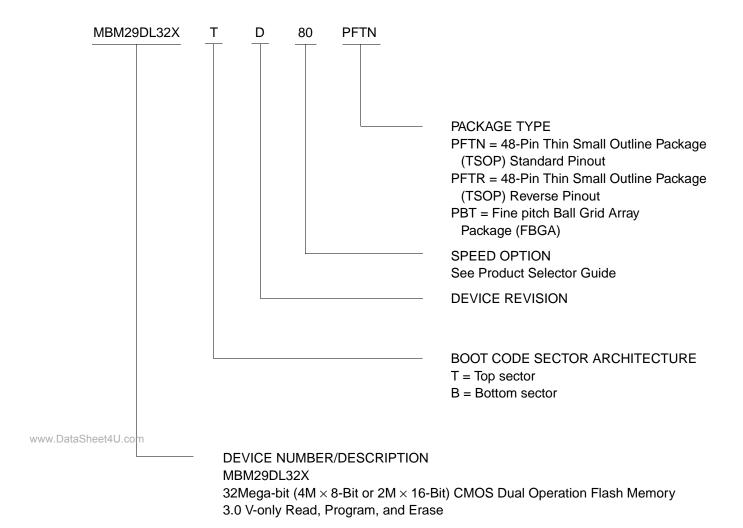




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Standard Products

Fujitsu standard products are available in several packages. The order number is formed by a combination of:

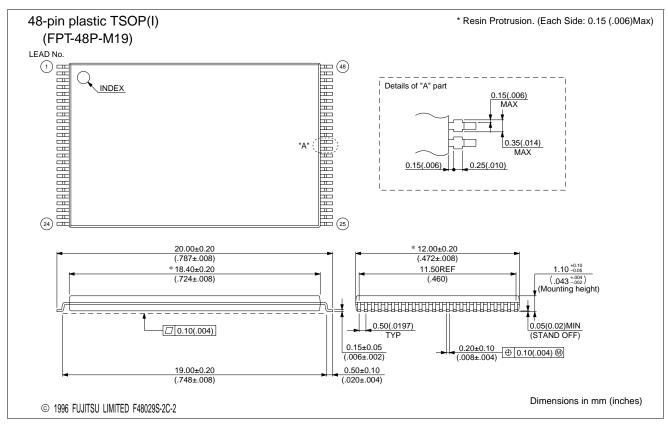


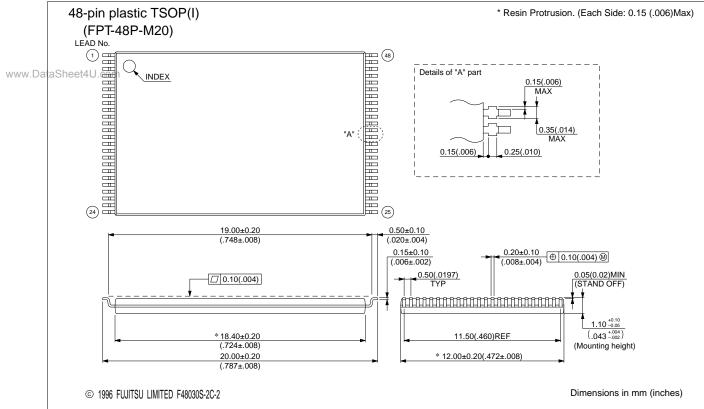
Valid Combinations		
MBM29DL321TD/BD		
MBM29DL322TD/BD	80 90 12	PFTN PFTR PBT
MBM29DL323TD/BD		
MBM29DL324TD/BD		

Valid Combinations

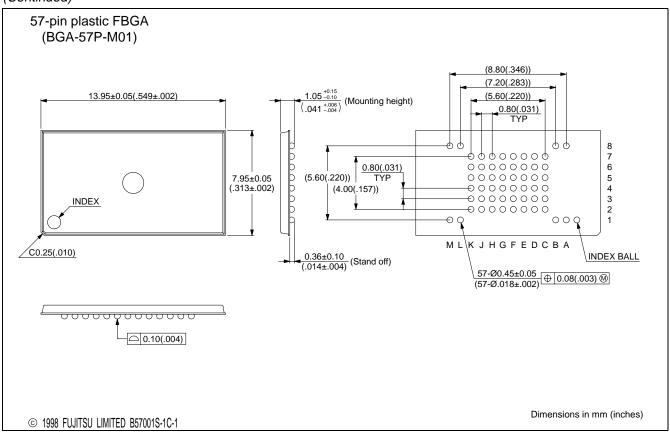
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local Fujitsu sales office to confirm availability of specific valid combinations and to check on newly released combinations.

■ PACKAGE DIMENSIONS





(Continued)



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